



University of
Nottingham

UK China Malaysia

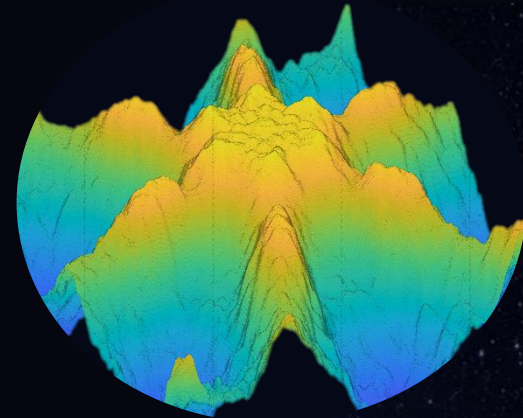
Layered Semiconductors with Inverted Mexican Hat Valence Band

A. Patanè

School of Physics and Astronomy, University of Nottingham, Nottingham, UK

Outline

- ❖ Semiconductors with Mexican hat valence band
- ❖ Ferroelectric semiconductors with Mexican hat valence band
- ❖ Challenges and Opportunities





**University of
Nottingham**

UK China Malaysia

**Nottingham Castle
& Robin Hood**
13th century



Founded in 1881
4 campuses in the UK

45,500 students
7,000 staff

International campuses
in Malaysia (1999)
and China (2004)



Nottingham, UK





University of
Nottingham

UK China Malaysia

Green's Mill



George Green 1793-1841

AN ESSAY
ON THE
APPLICATION
MATHEMATICAL ANALYSIS TO THE THEORIES OF
ELECTRICITY AND MAGNETISM.

BY
GEORGE GREEN.

$$\int \frac{\rho d\sigma}{r} = \frac{1}{4\pi} \left\{ \int d\sigma \bar{V} \left(\frac{d\frac{1}{r}}{dw} \right) - \int \frac{d\sigma}{r} \left(\frac{d\bar{V}}{dw} \right) \right\}$$

Nottingham;

PRINTED FOR THE AUTHOR, BY T. WHEELHOUSE.

SOLD BY HAMILTON, ADAMS & Co. 25, PATERNOSTER ROW; LONGMAN & Co.; AND W. JOY, LONDON;
J. DEIGHTON, CAMBRIDGE;

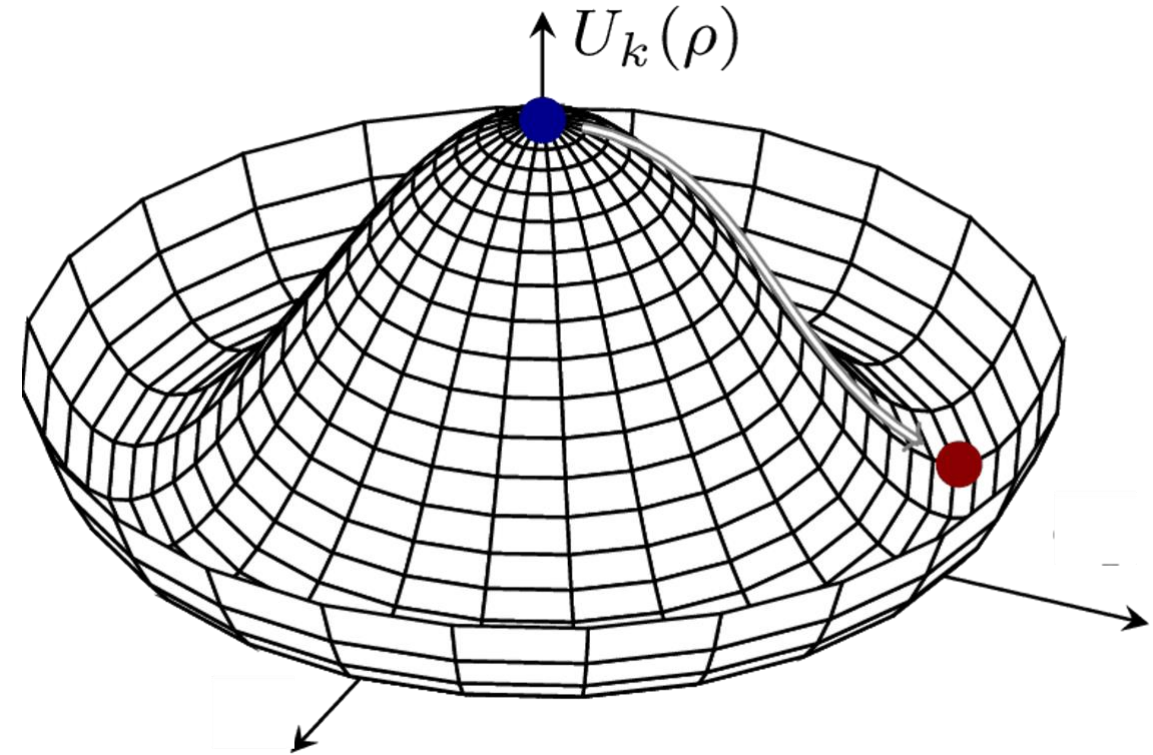
AND S. BENNETT, H. BARNETT, AND W. DEARDEN, NOTTINGHAM.

1828,

The 1828 essay introduced the concept of **potential** and **Green's function**, the foundation of electromagnetism and many discoveries across disciplines.

Mexican Hat-Shaped Bands

- ❖ **Van Hove singularity** in the density of states can induce strong *electron-electron interactions*, *ferromagnetic phases*, *superconducting pairing*...
- ❖ **Negative or positive electron effective mass**, dependent on energy.



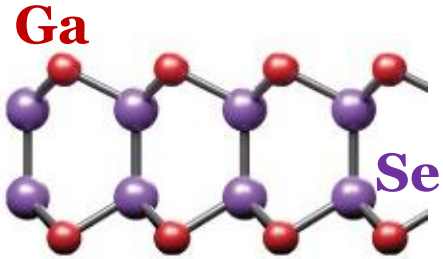
Hirsch et al. *Phys. Rev. Lett.* 56 (1986)

Stauber et al *Phys. Rev. B* 75 (2007)

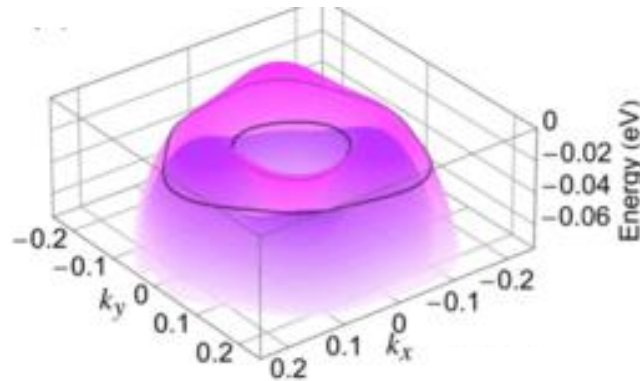
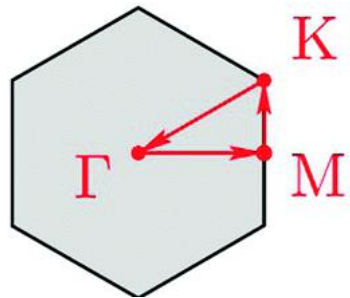
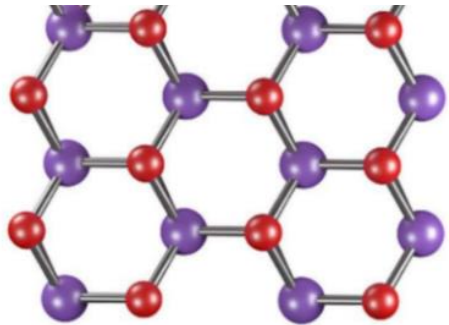
Cappelluti et al. *Phys. Rev. Lett.* 98 (2007)

Inverted Mexican-Hat Valence Band

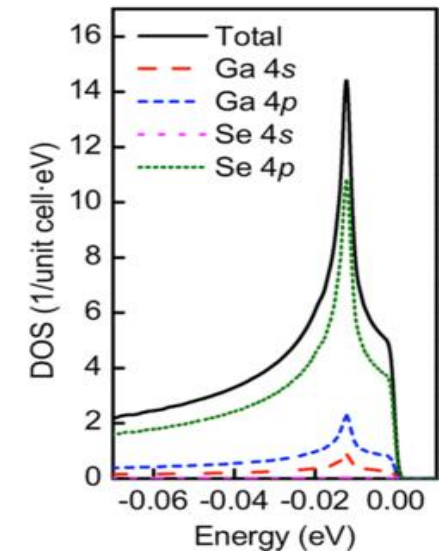
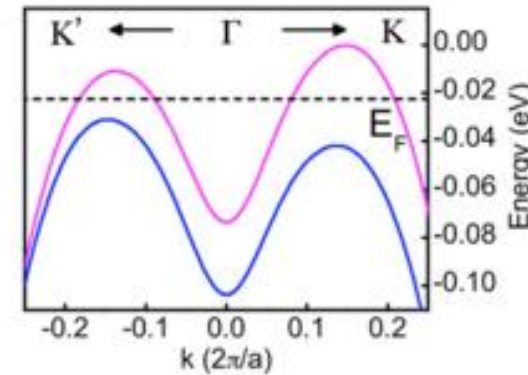
Monolayer GaSe: Tuneable Magnetism by Doping



- ❖ Large average spin magnetic moment per carrier (up to $\sim 1.0 \mu_B$)
- ❖ Itinerant magnetism from exchange splitting of electronic states near the top of the VB/van Hove singularity.



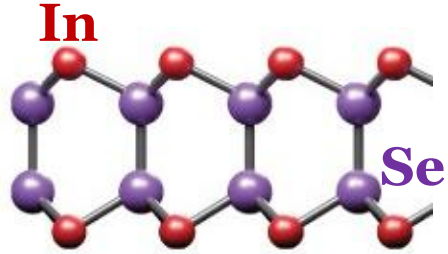
spin-up/-down states for $p \sim 10^{14}/\text{cm}^2$



Van Hove singularity in DOS

Inverted Mexican-Hat Valence Band

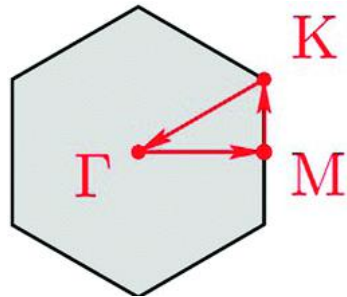
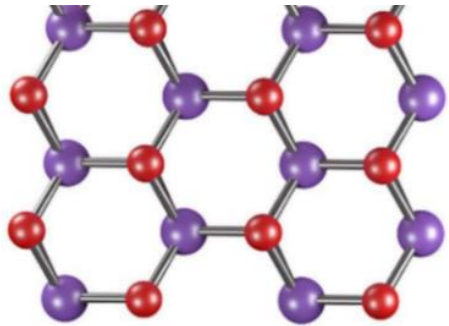
Monolayer InSe: Charge Instabilities by Doping



❖ Strong hole interaction with acoustic phonons

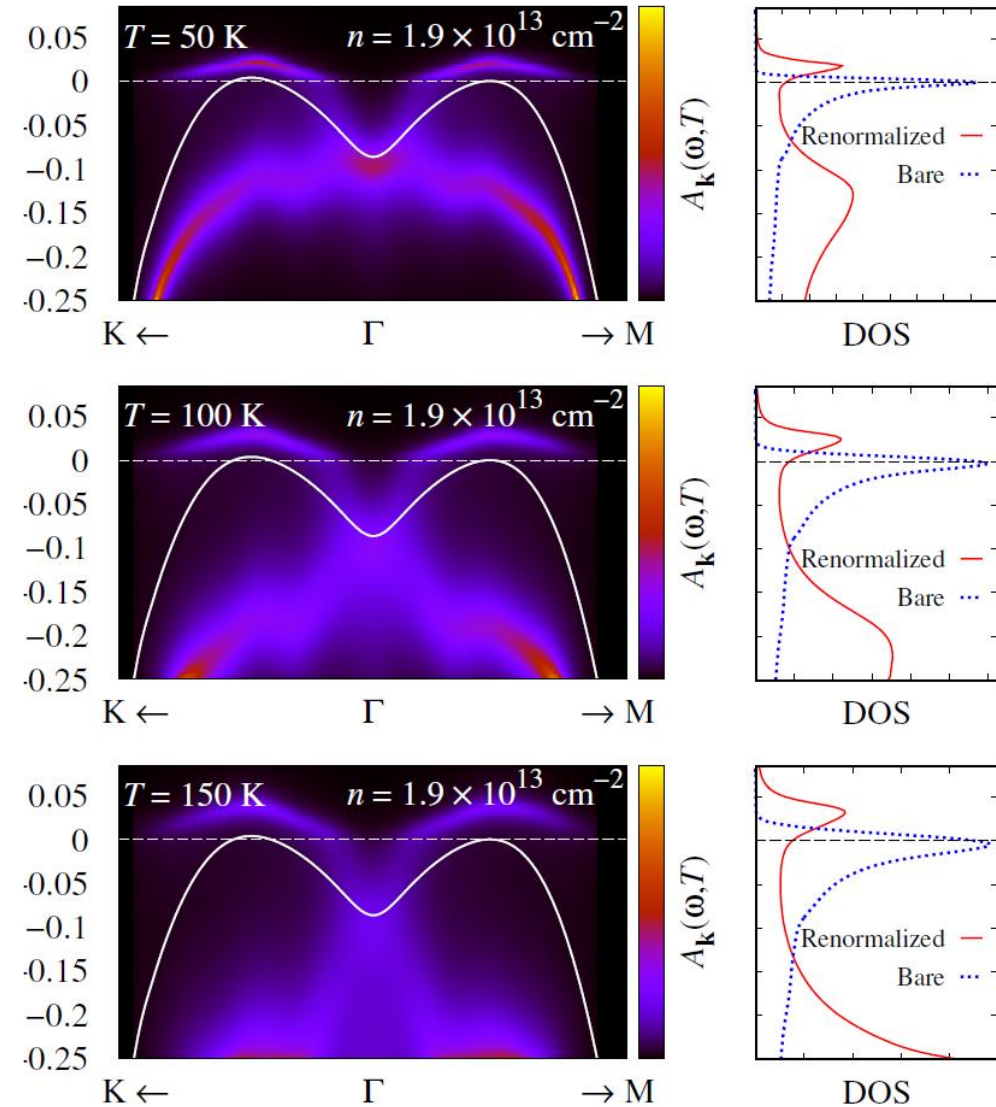
❖ Quasi-particle states near the Fermi surface

❖ Charge density waves and ferromagnetic order



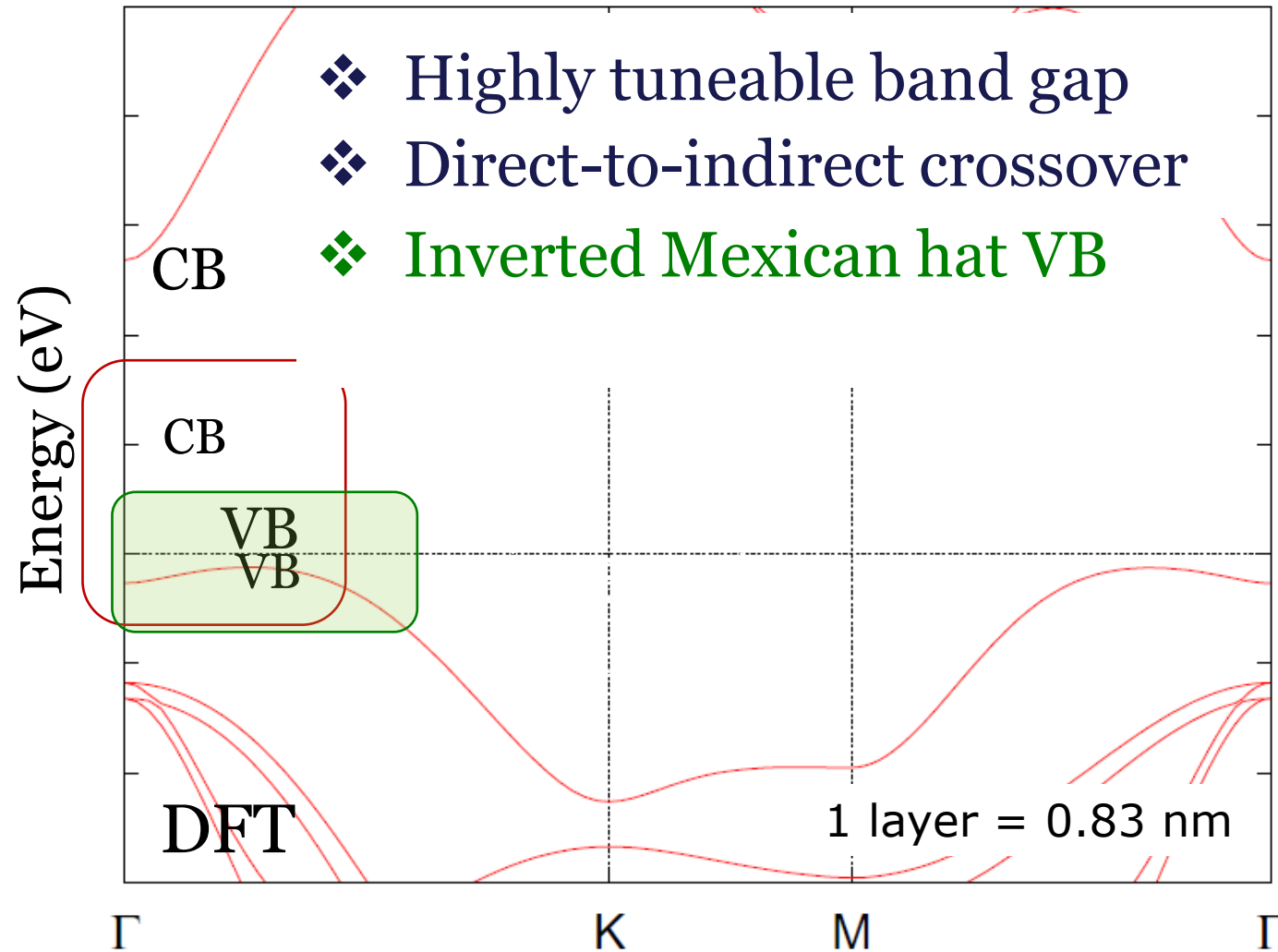
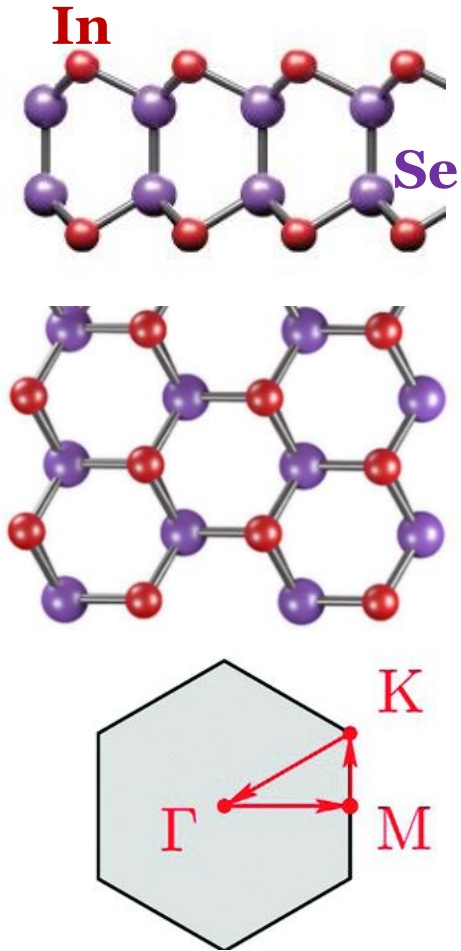
Lugovskoi et al. *Phys. Rev. Lett.* 2019

Stepanov et al. *npj Comp. Mat.* 2022

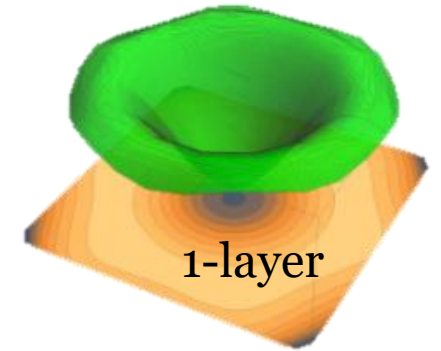


Tuneable Band Structure

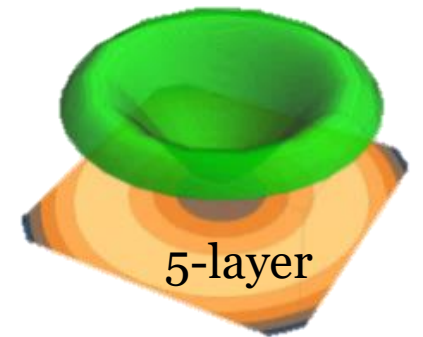
From Monolayer to Multiple-layer InSe



Inverted Mexican hat VB



1-layer

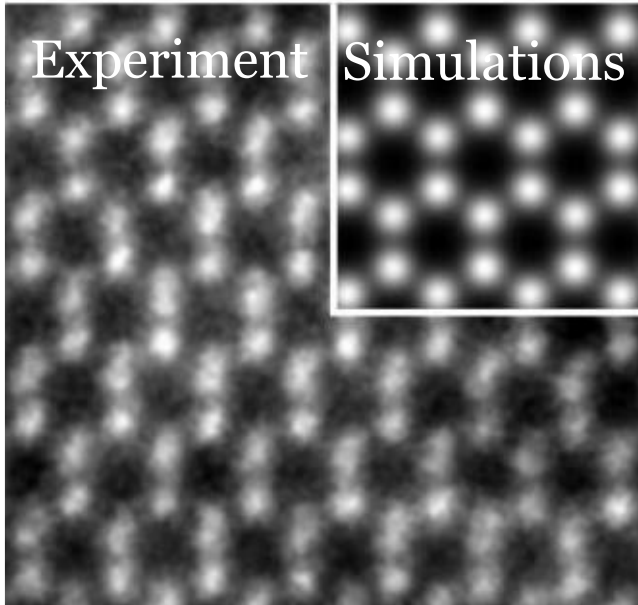


5-layer

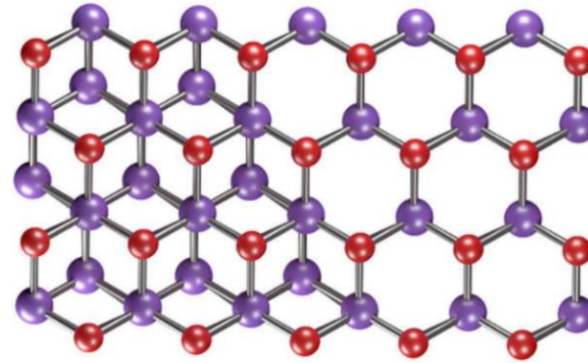
2D Semiconductors, 2SEM

Metal III: Ga, In

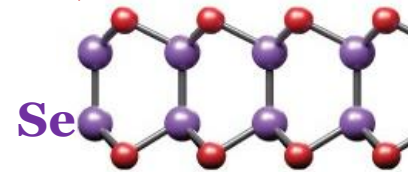
Chalcogen VI: Se



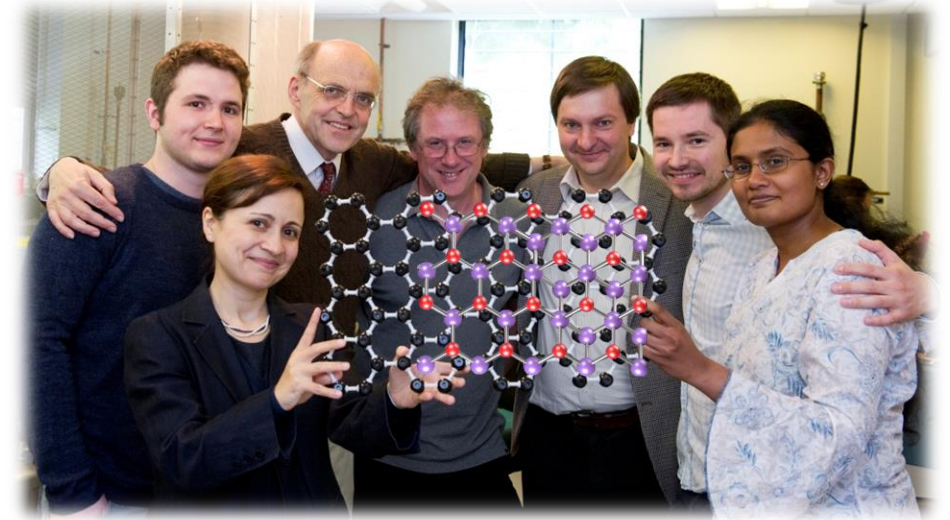
Hopkinson et al. *ACS Nano* 2019



In, Ga



Se

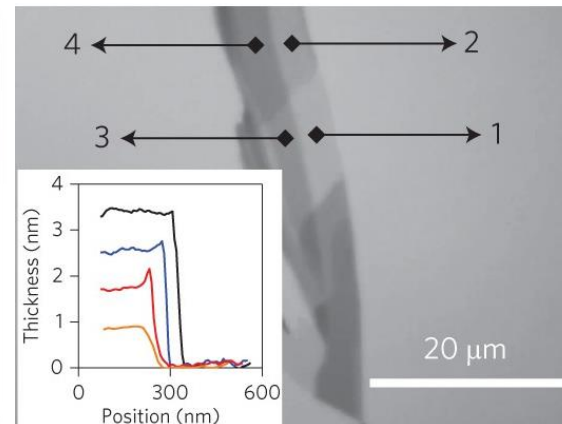
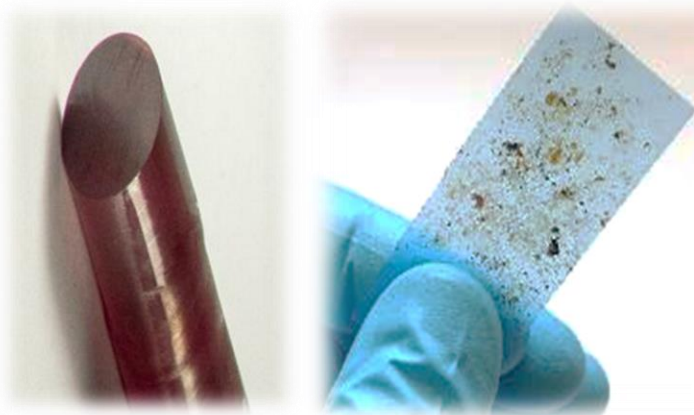


- ❖ High electron mobility (e.g. InSe)
- ❖ Tuneable band gap energy
- ❖ Optical anisotropy
- ❖ Ferroelectricity
- ❖ Elasticity

Mudd et al. *Adv. Mat.* 2013

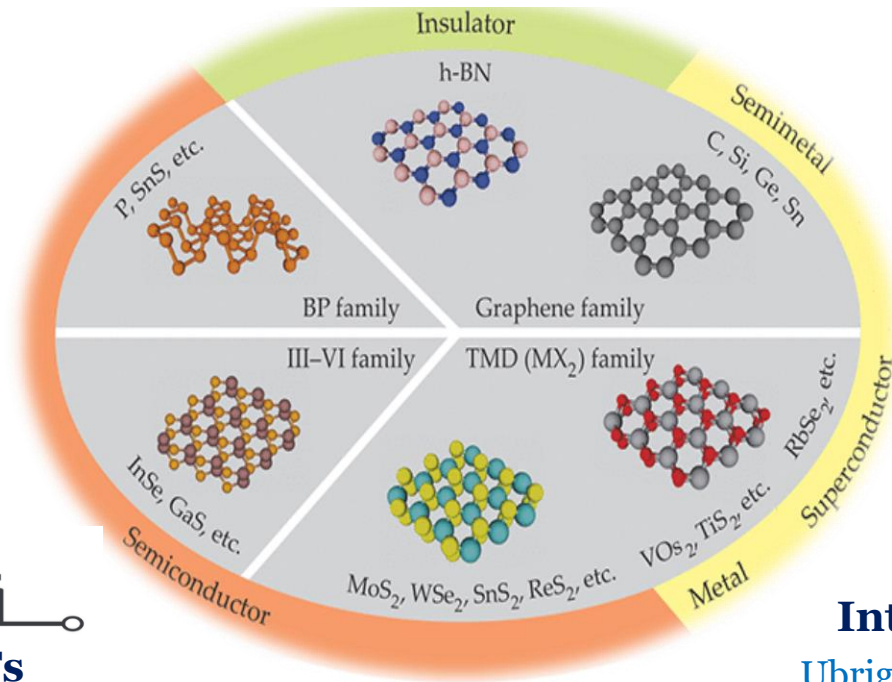
Mudd et al. *Adv. Mat.* 2015

Bandurin et al. *Nature Nano.* 2017



2SEM Heterostructures

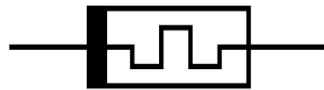
Ajayan et al *Phys. Today* 2016



FETs

Bandurin et al.

Nature Nano. 2017



Ferroelectricity

Xie et al. *2D Mat.* 2021

Felton et al. *Nature Com.* 2025



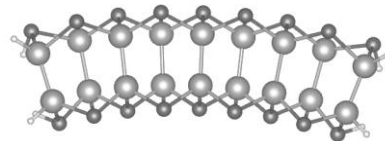
Quantum Hall Sensors

Kudrynskyi et al. *PRL* 2017



Interlayer Excitons

Ubrig et al. *Nature Mat.* 2020

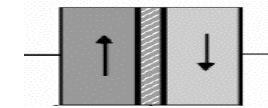
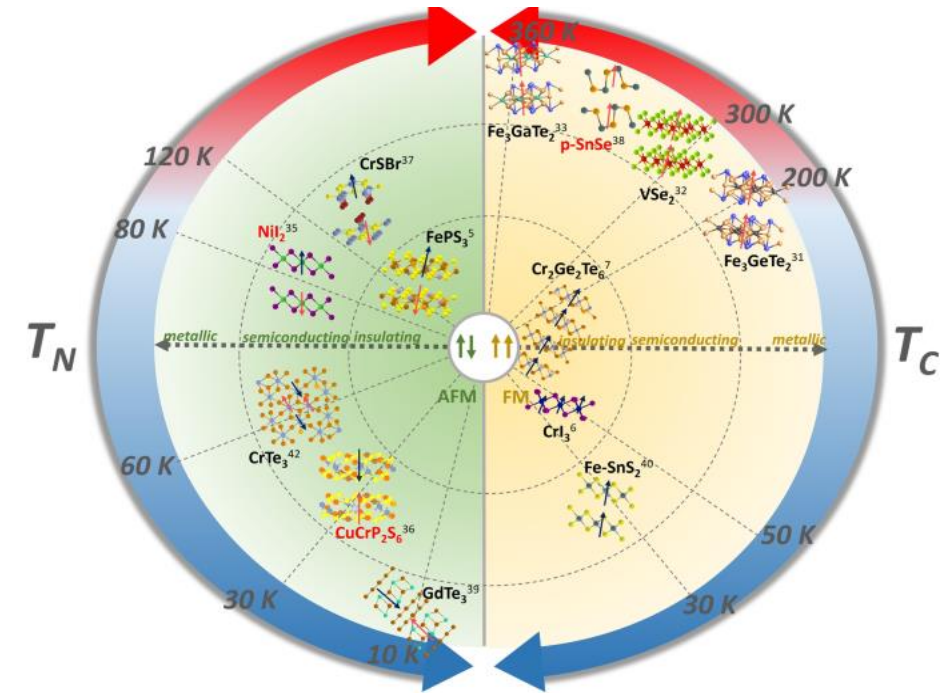


Flexible electronics

Blundo et al. *Nano Lett.* 2025

Barker et al. *npj Flex. El.* 2025

Zhang et al. *npj Spintronics* 2024



Spin valves

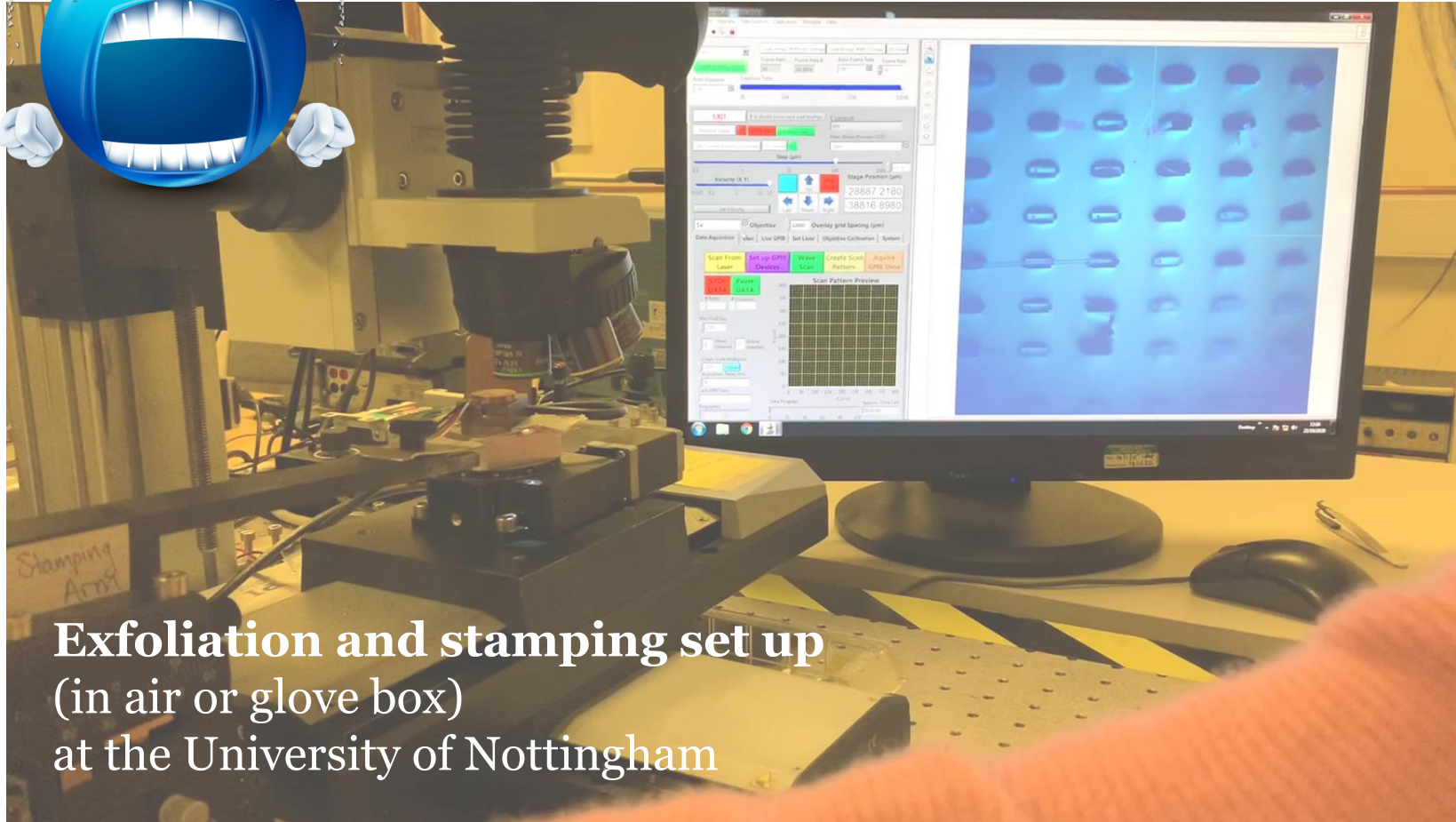
2D Magnetic/TMD/MC

Zhu et al. *Adv. Mat.* 2021

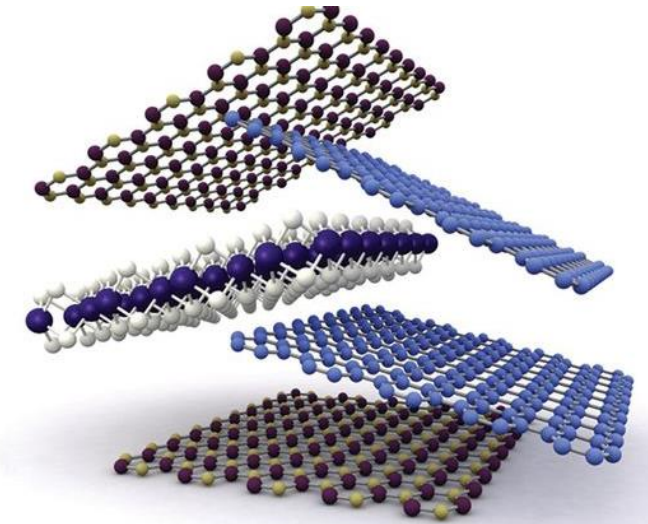
Zhu et al. *Nature Com.* 2025

Making 2SEM

Mechanical exfoliation and stamping of 2SEM



Exfoliation and stamping set up
(in air or glove box)
at the University of Nottingham



Novoselov et al. *Science* 2016

- ❖ No scalability
- ❖ Contamination
- ❖ Limited control of size, composition, doping...

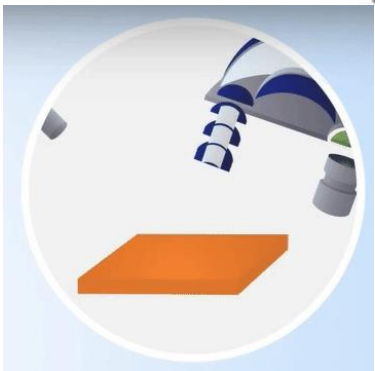
Epitaxial 2SEM

EPI₂SEM: EPItaxial growth and In-situ analysis of **2SEM**

2SEM: 2D semiconductors

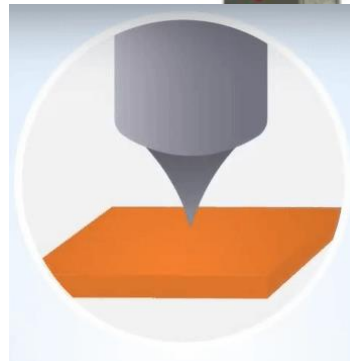
3-chamber cluster in ultra high vacuum

**Electron
Spectroscopy
for
Chemical
Analysis**



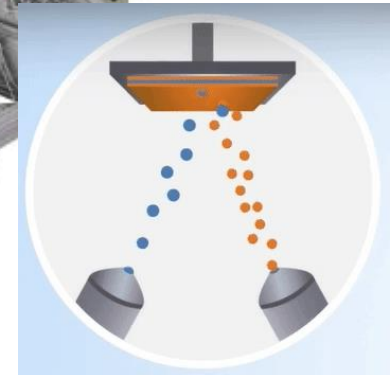
Probing bonds
and band
structures
XPS
XPEEM
PEEM
 μ -ARPES

**Scanning Probe
Microscopy**



**Molecular Beam
Epitaxy**

Epitaxy in UHV
(up to 3" wafers)
for growth of
2SEM with atomic
resolution
Focus on
In, Se, Ga...



£3.2 m UKRI Strategic Equipment Award 2020-24 (with Scienta Omicron/MBE Komponenten)

EPI₂SEM: “Cooking and Tasting”

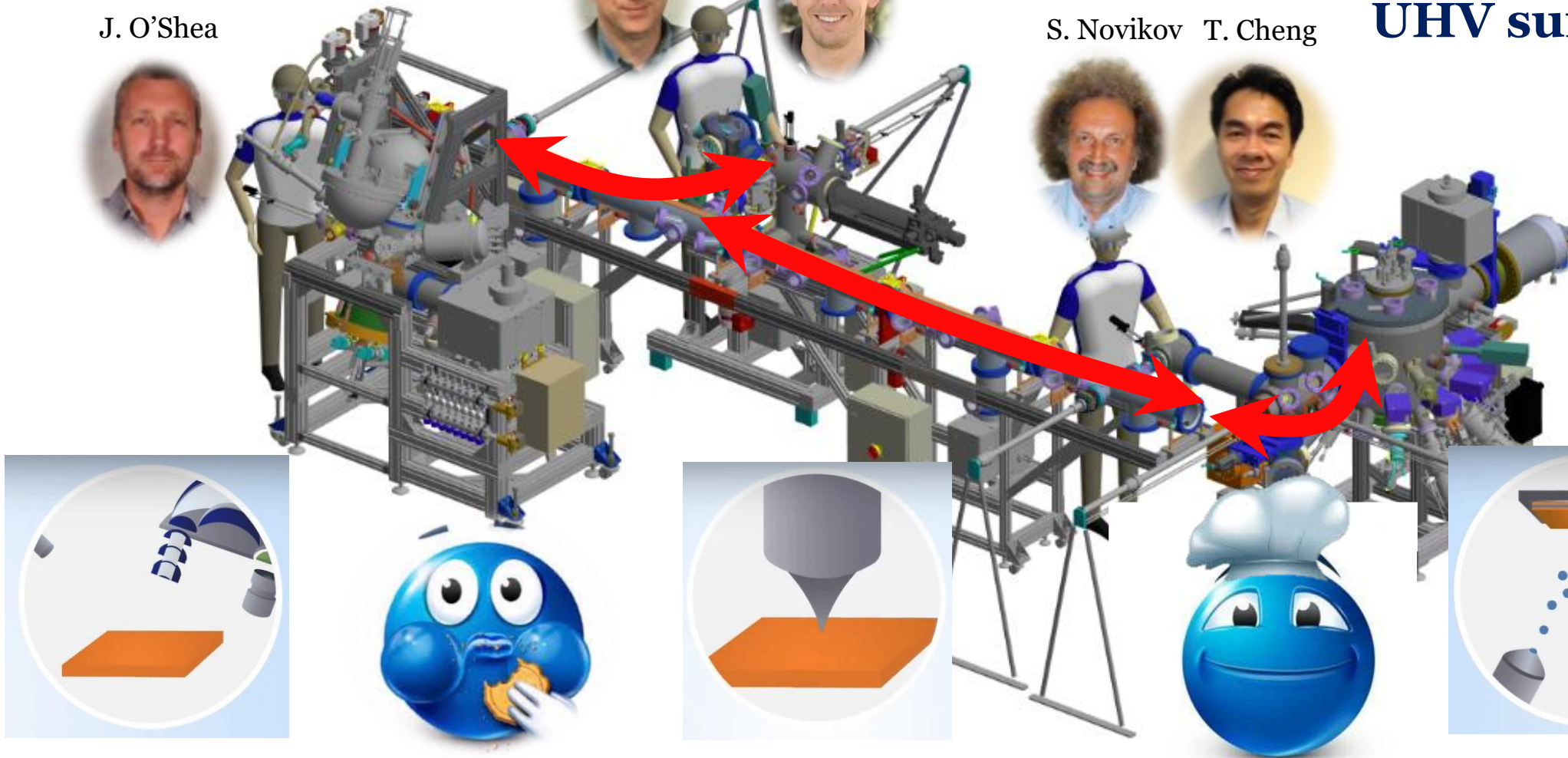
P. Beton

J. Bradford

Link to other
facilities by
UHV suitcase

J. O'Shea

S. Novikov T. Cheng



£3m UKRI Strategic Equipment Award 2020-24 (with Scienta Omicron/MBE Komponenten)

2021-22 Installation of EPI₂SEM



<https://www.youtube.com/watch?v=mtXWhMOs9D4>

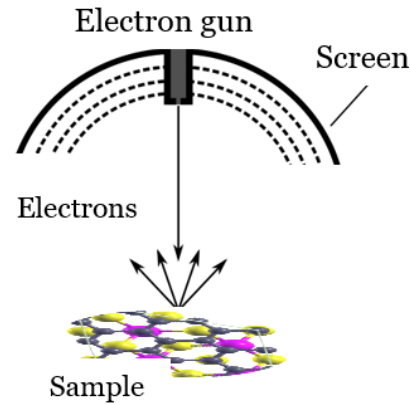
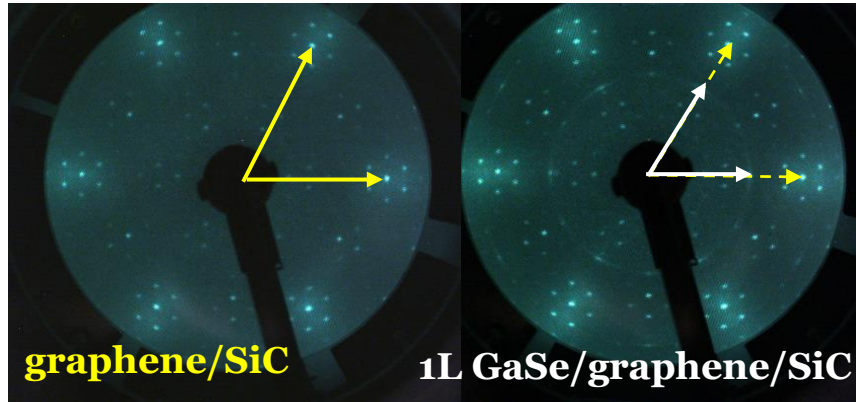
<https://www.youtube.com/watch?v=GHCxEDMh3Ro>



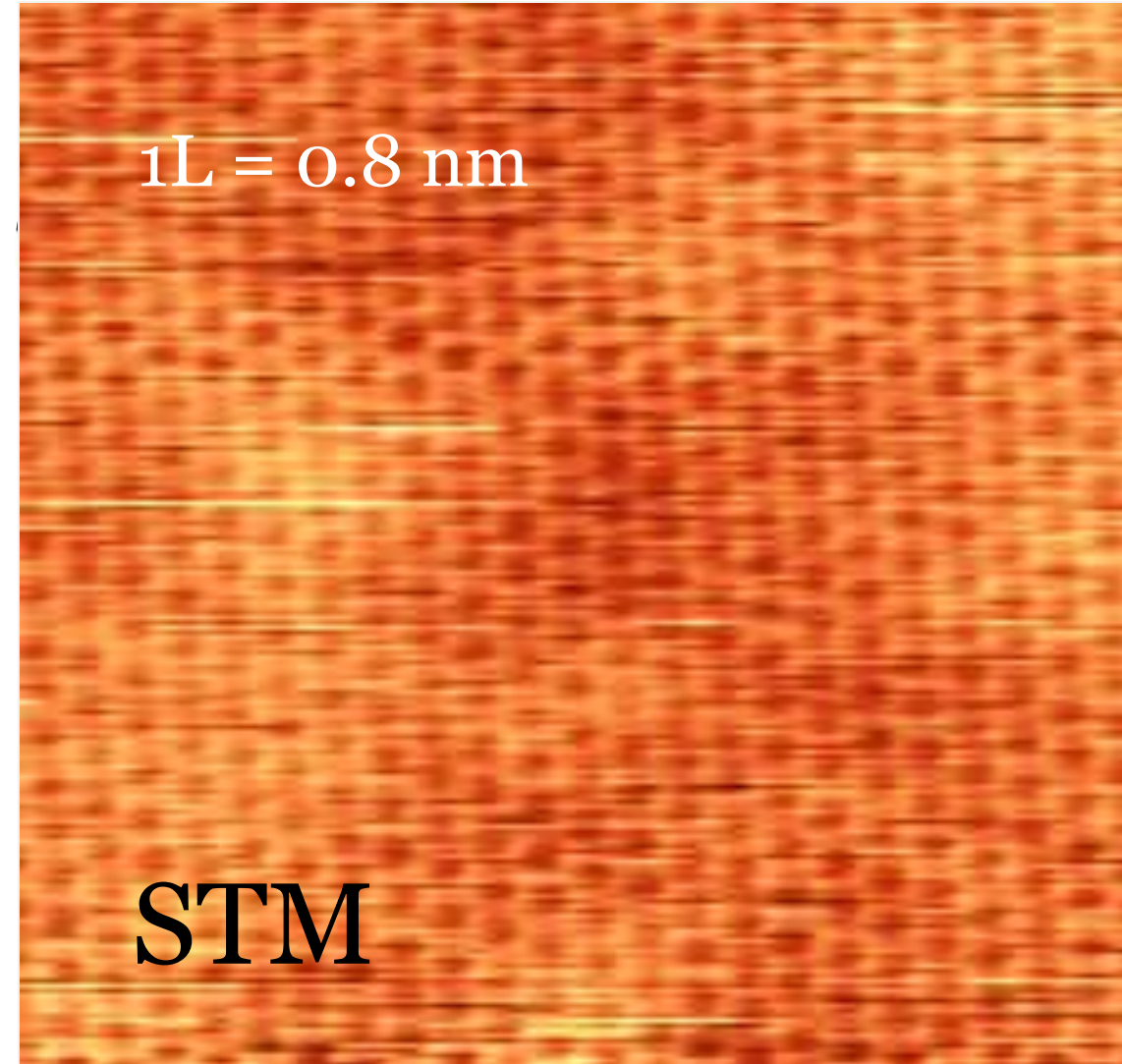
2D GaSe on Graphene

Epitaxy of 2D GaSe on epitaxial graphene

Low-energy electron diffraction (LEED)



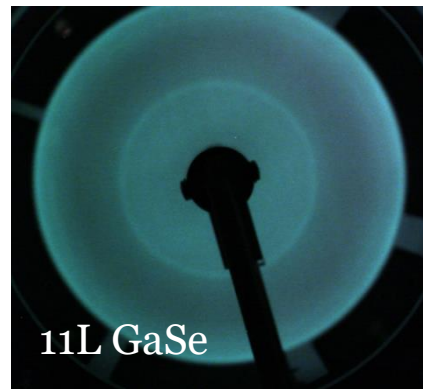
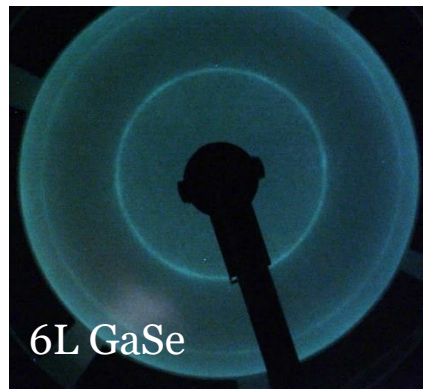
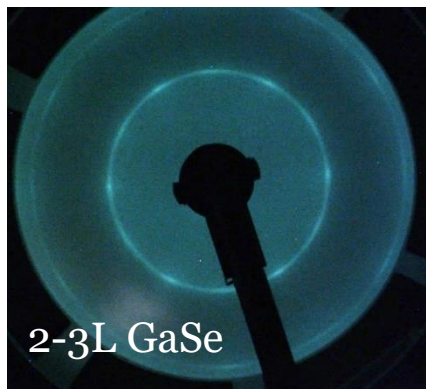
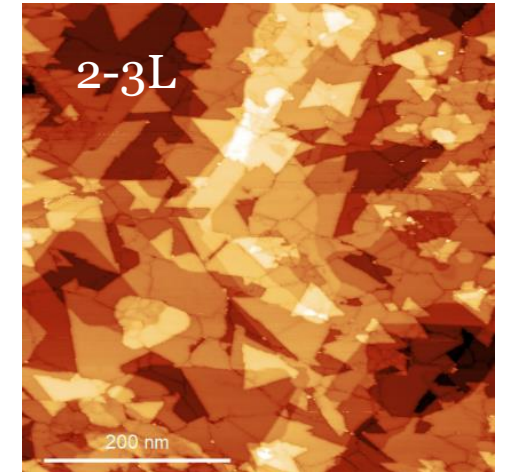
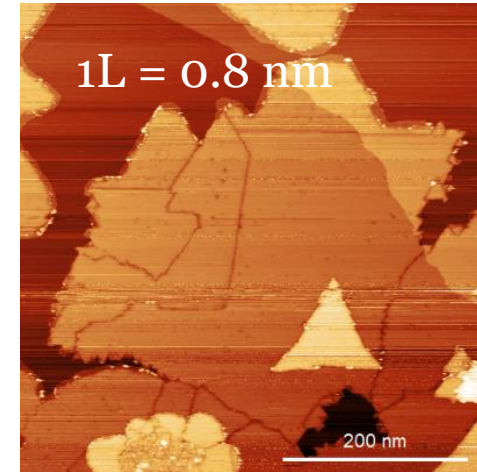
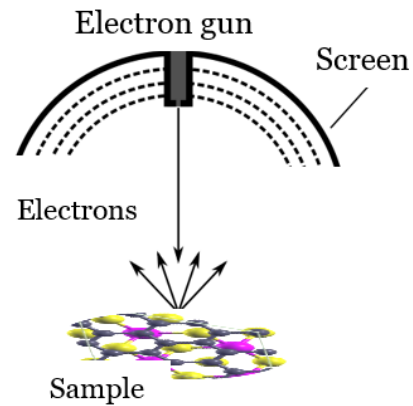
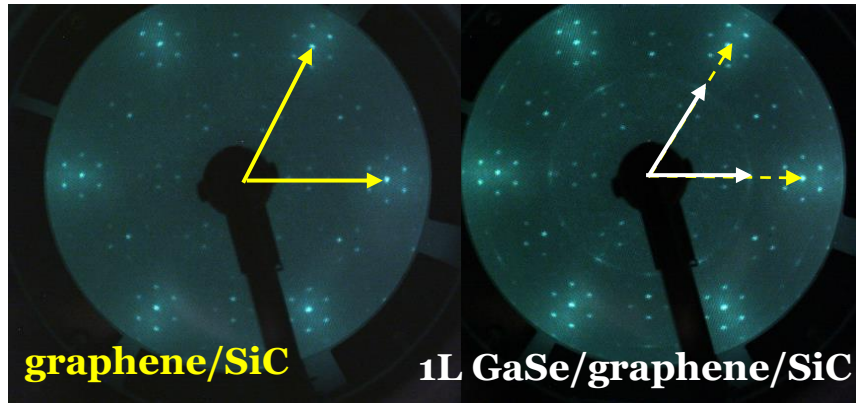
Crystallinity and in-plane alignment of 1 layer (1L = 0.8 nm) GaSe with graphene



2D GaSe on Graphene

Epitaxy of 2D GaSe on epitaxial graphene

Low-energy electron diffraction (LEED)

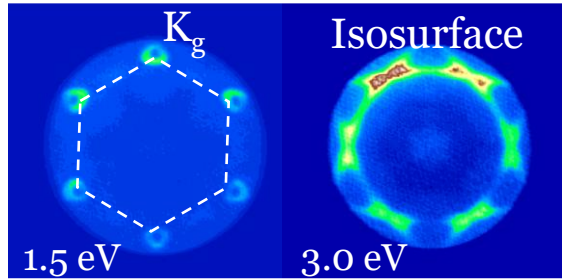


Orientation-disorder in thick layers
In-plane alignment not detected in thicker ($> 3L$) GaSe due to the small penetration depth of the electron beam and grains with smaller (100 nm) lateral dimensions.

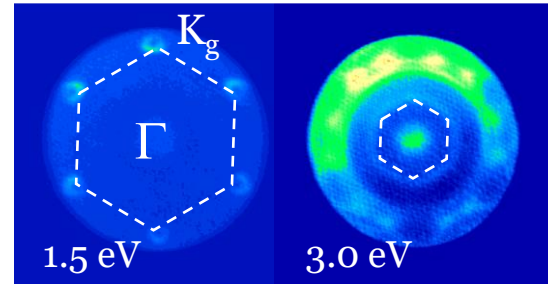
GaSe: Band Structure and Symmetry

Angle Resolved Photoemission Spectroscopy, ARPES

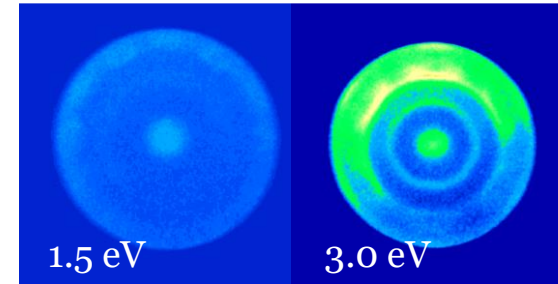
graphene



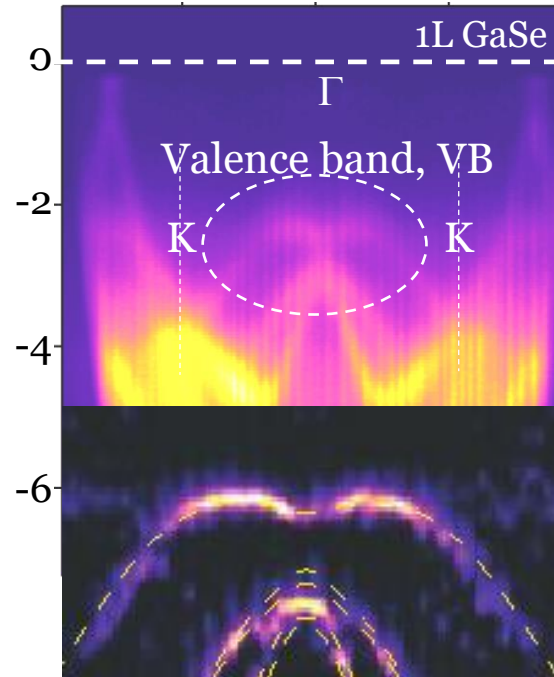
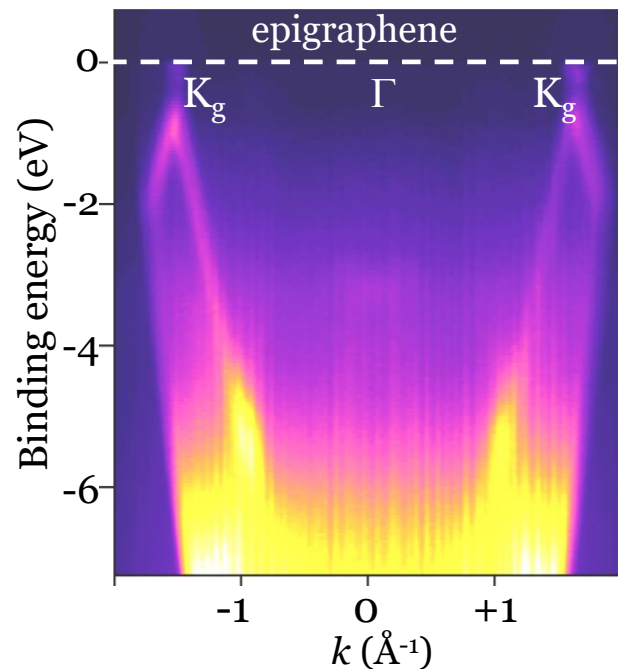
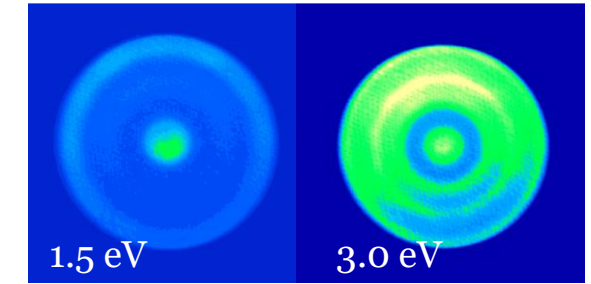
1L GaSe



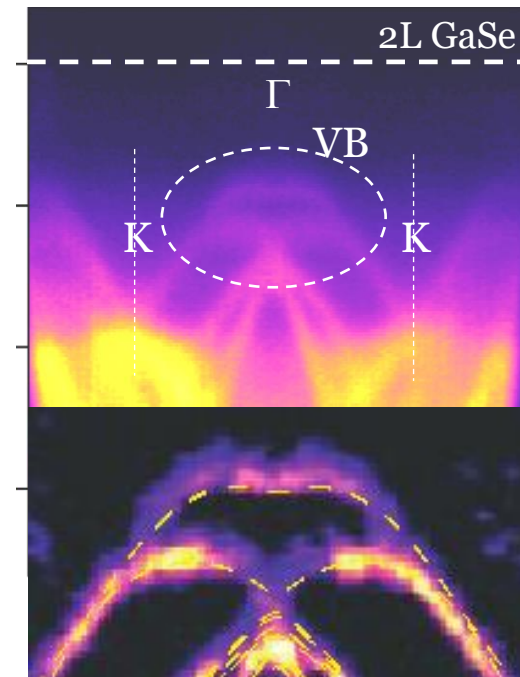
2L GaSe



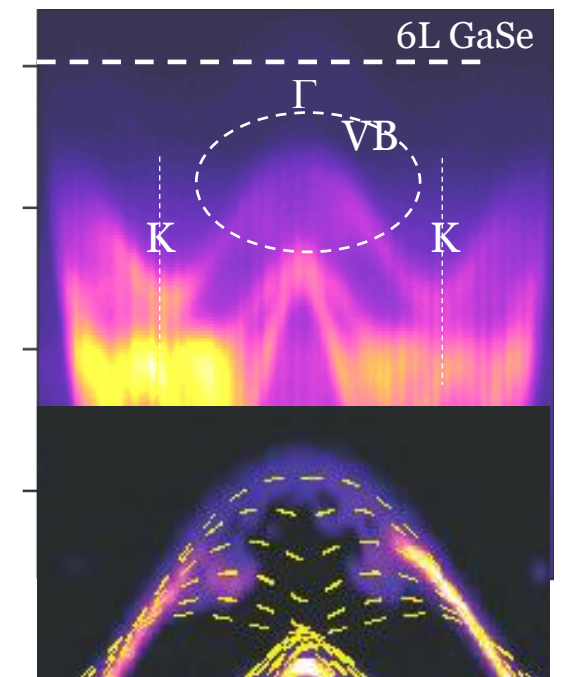
6L GaSe



Mexican Hat VB



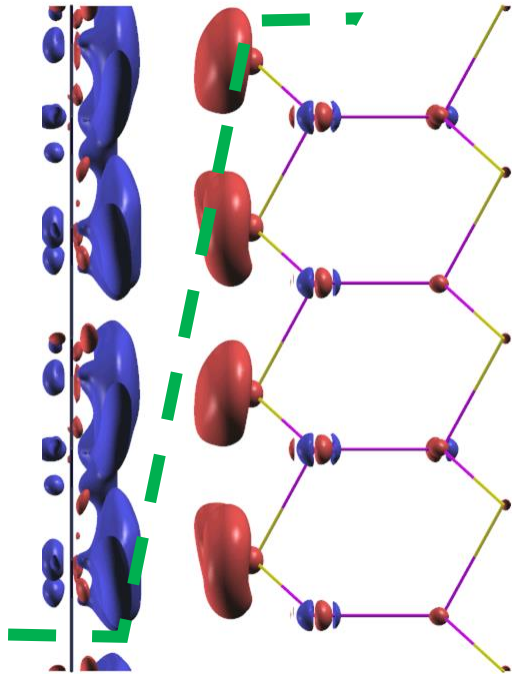
Mexican Hat VB



Parabolic VB

Interfacial Charge Dipole

Charge Dipole



Graphene

GaSe

Blue = fewer electrons

Red = more electrons

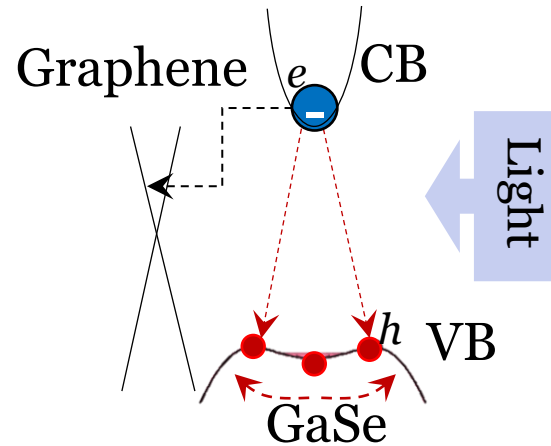
Built in potential

$$\Delta\phi = 0.25 \text{ eV}$$

Modelled by DFT

Measured by UPS

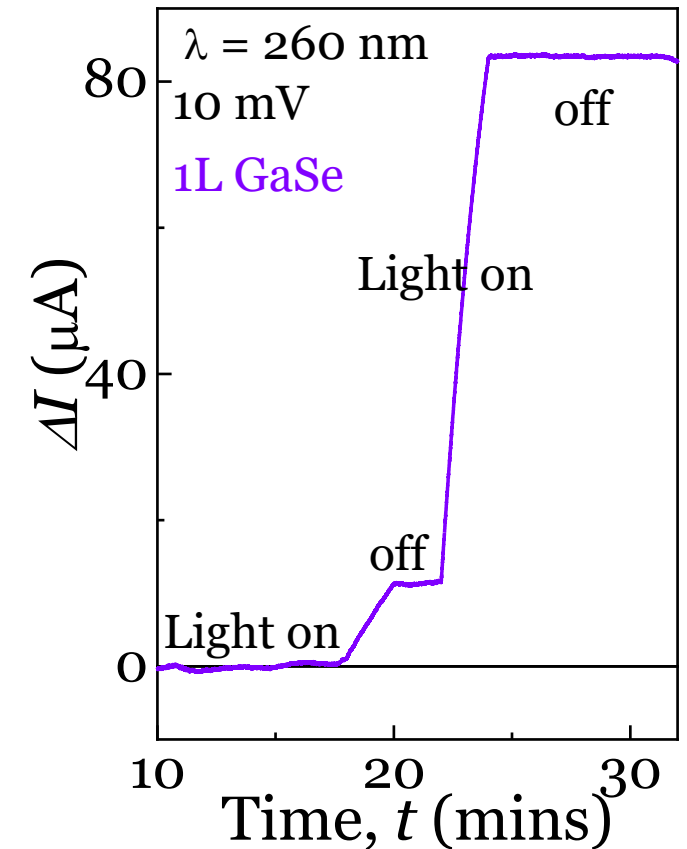
Effects of Light on graphene



- ❖ e-h created in GaSe
- ❖ Electrons transfer to graphene
- ❖ Holes localized in GaSe

Photo-memory

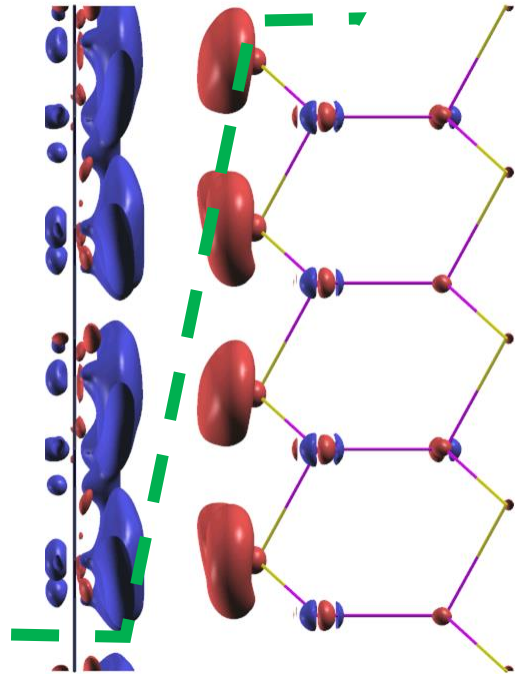
Persistent photocurrent in graphene



Bradford et al. *Small* 2024

Interfacial Charge Dipole

Charge Dipole



Graphene

GaSe

Blue = fewer electrons

Red = more electrons

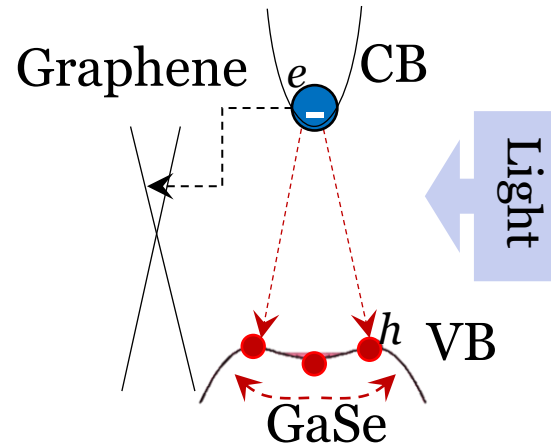
Built in potential

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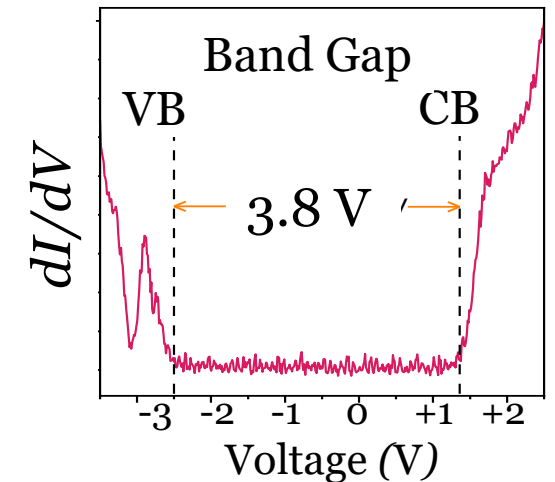
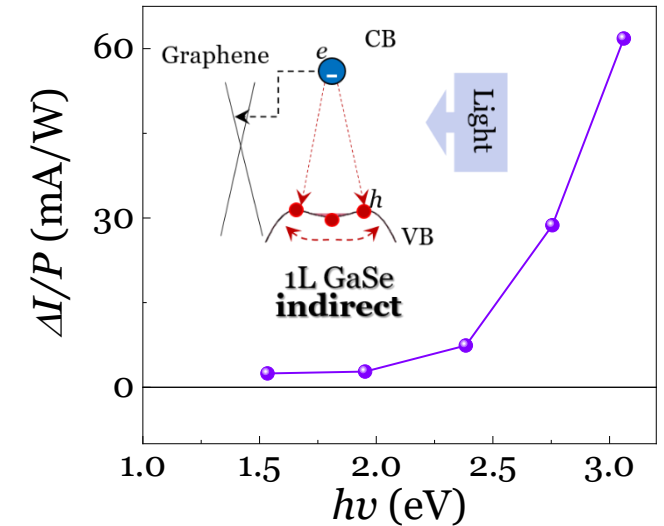
Measured by UPS

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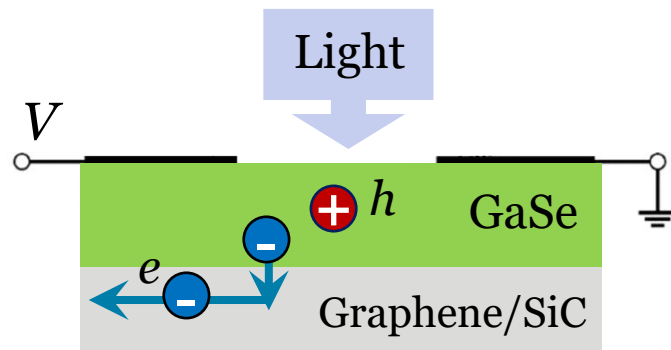
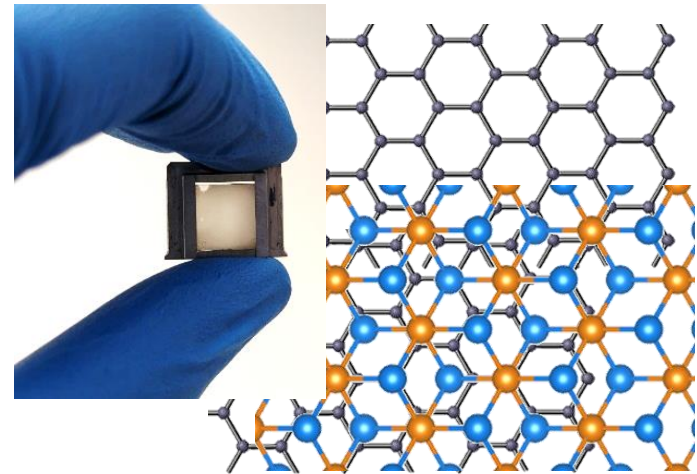
Photo-memory



Bradford et al. *Small* 2024

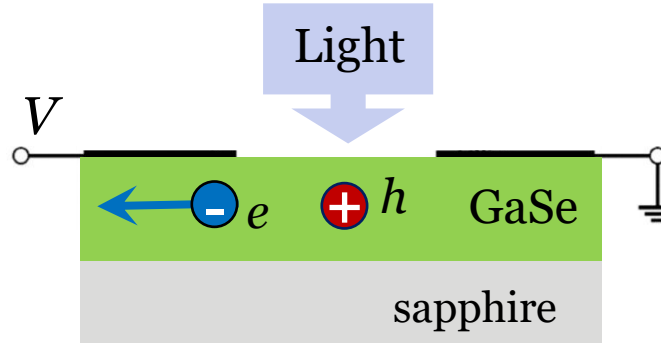
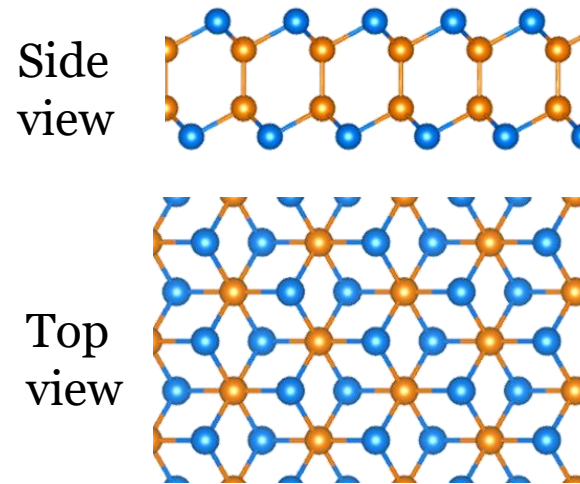
VIS-UV Photonics

GaSe/graphene/SiC



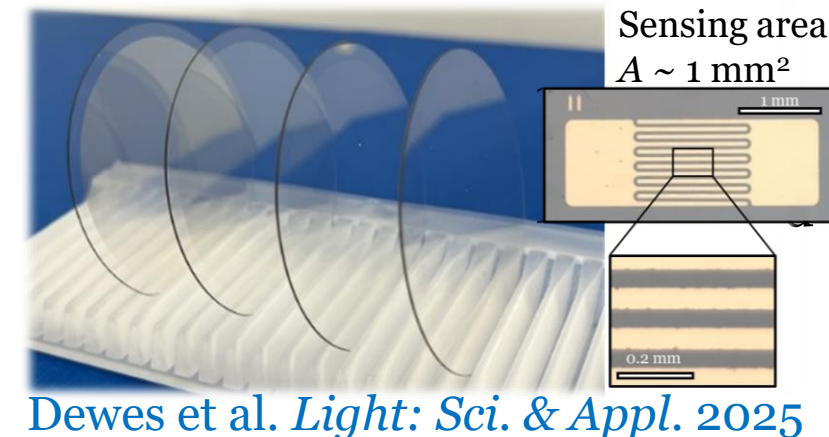
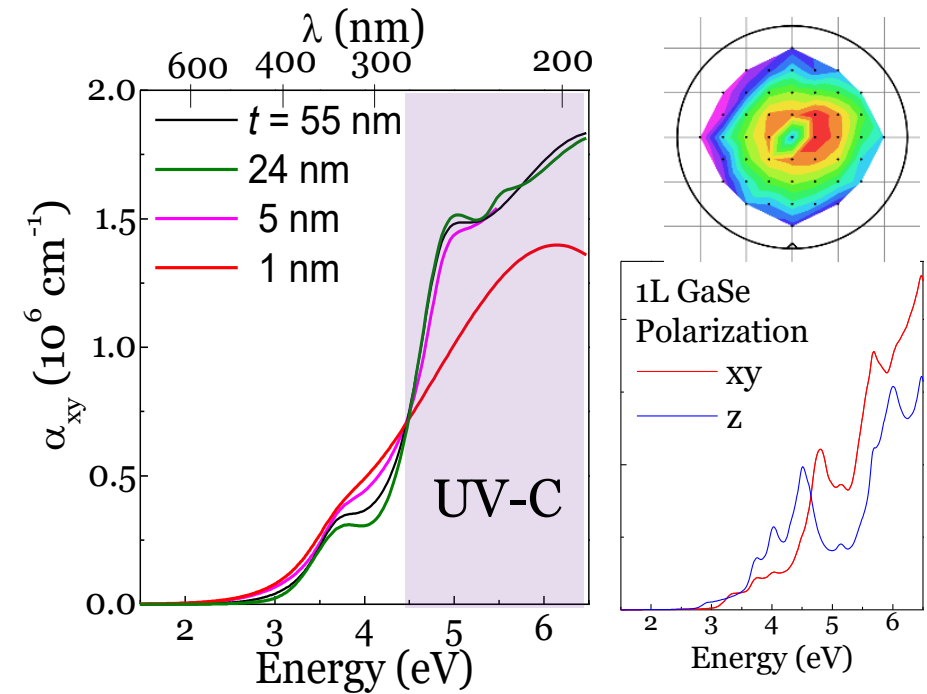
GaSe: Optical channel
 Graphene: Transport channel
 Bradford et al. *Small* 2024

GaSe/sapphire



GaSe: Optical & Transport channel
 Shiffa et al. *Small* 2024

Ellipsometry: Absorption

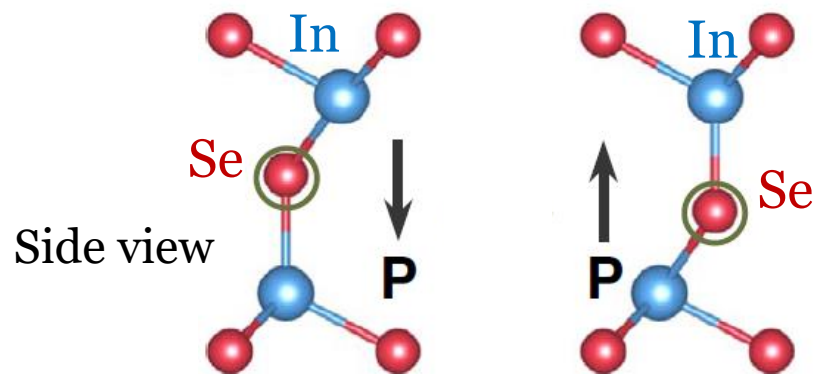


Dewes et al. *Light: Sci. & Appl.* 2025

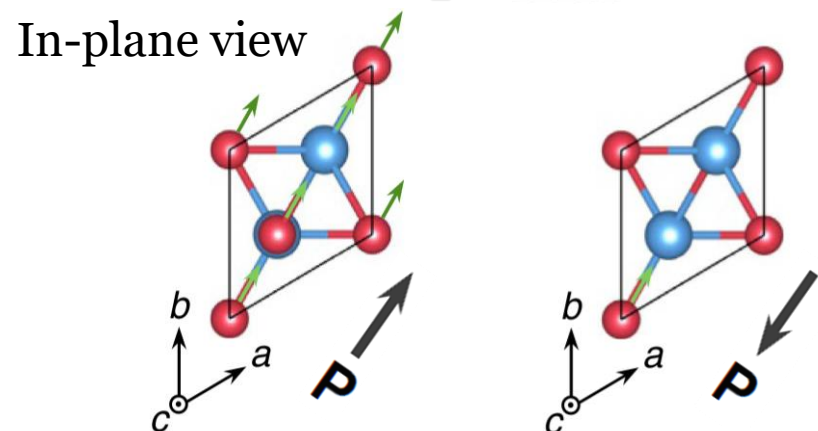
Ferroelectric In_2Se_3

Spontaneous electric polarization P in non-centrosymmetric In_2Se_3

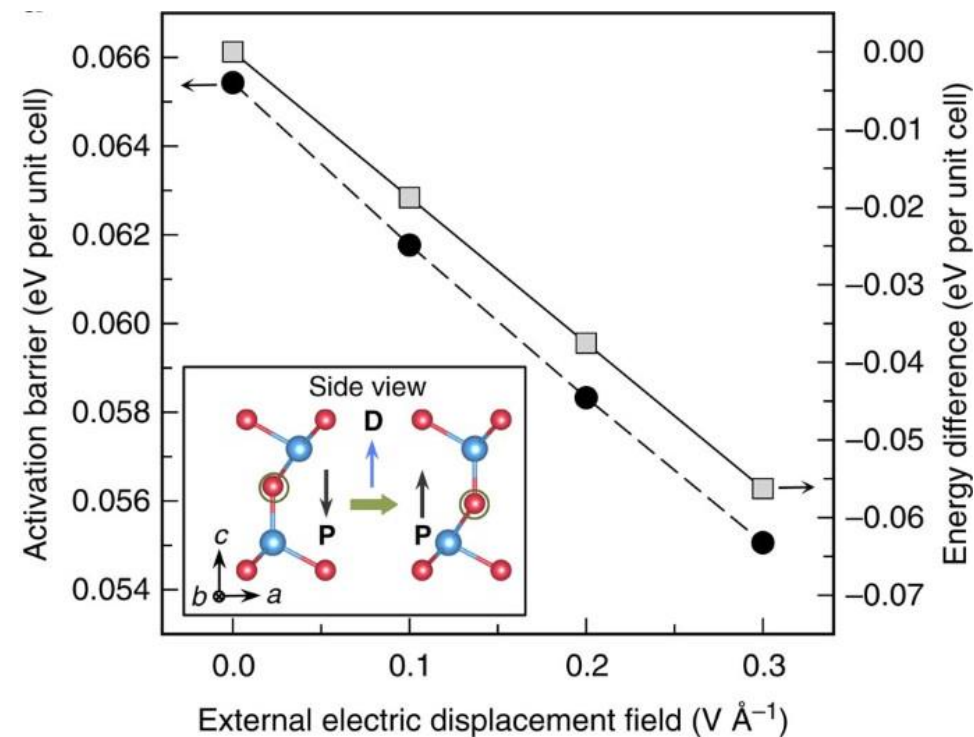
Out-of-plane P



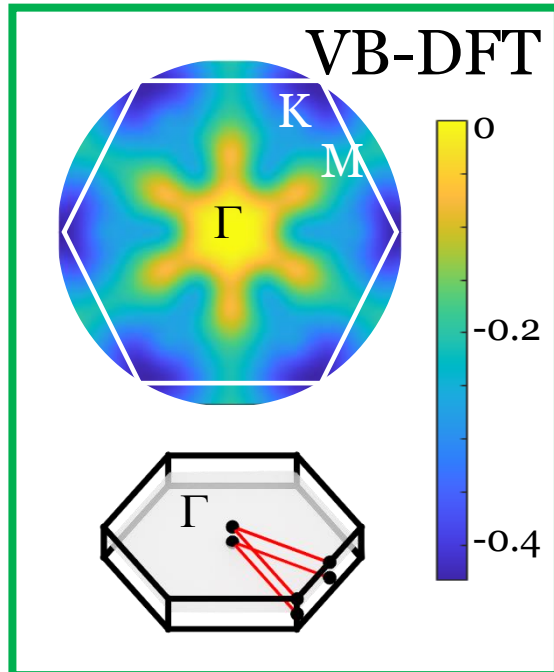
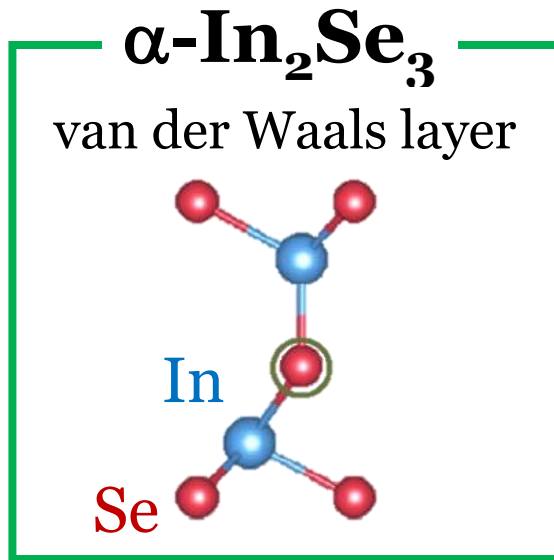
In-plane P



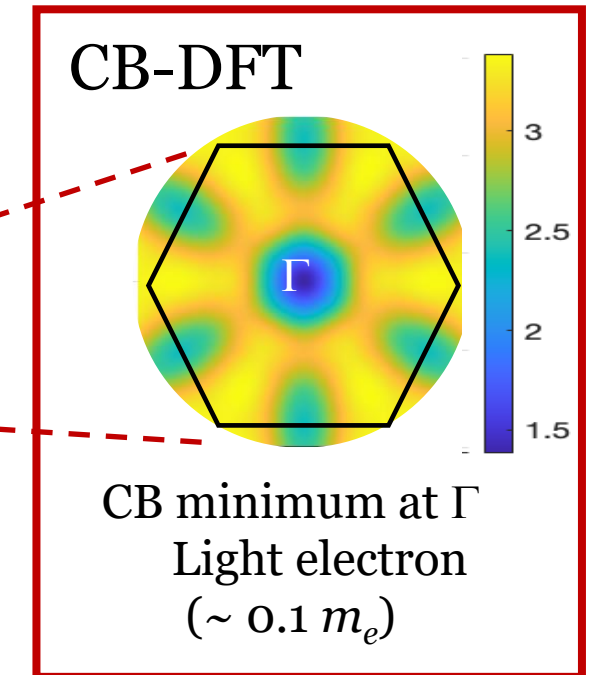
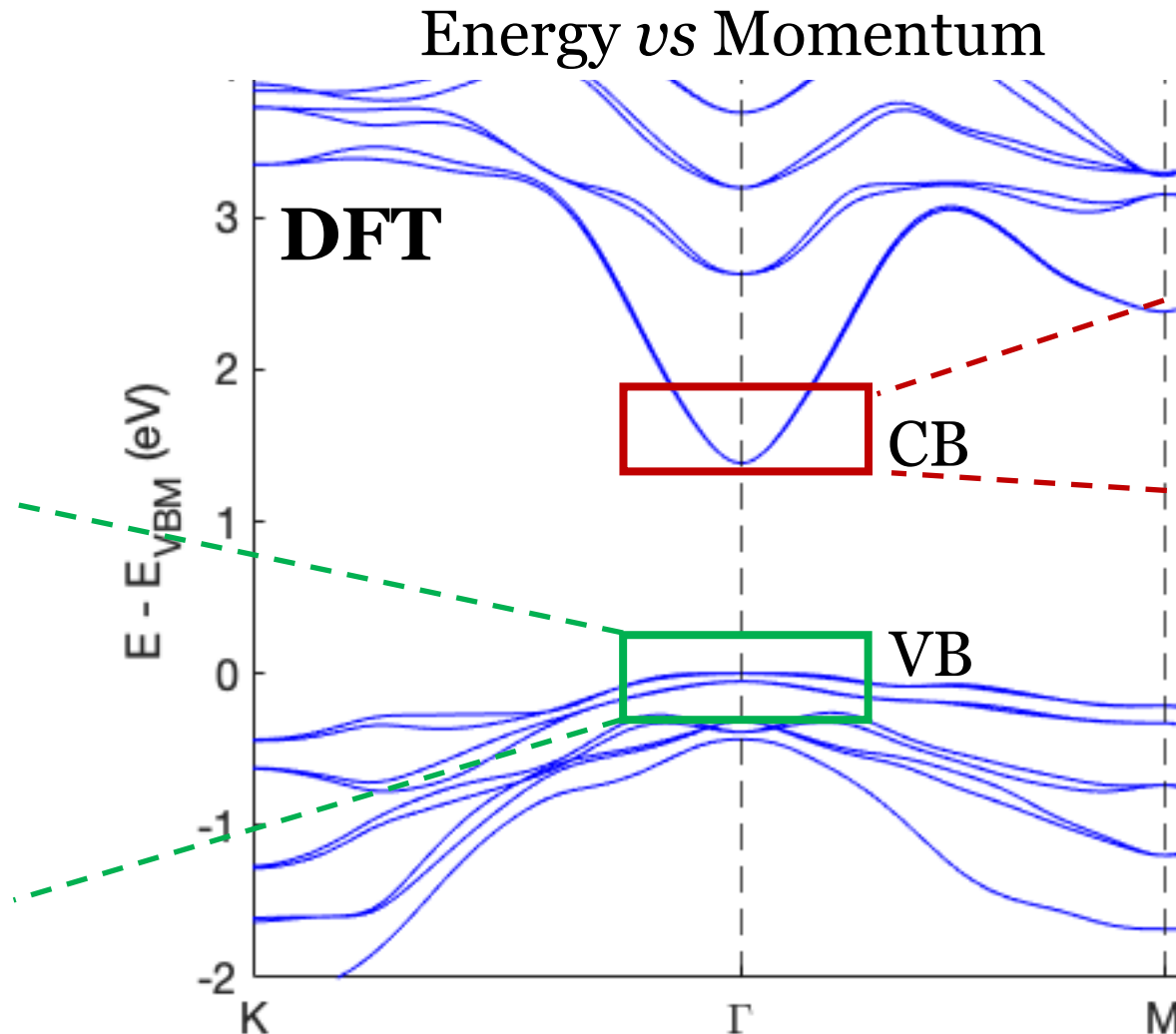
- ❖ The electric field lifts the degeneracy of the two polarized states, thus reversing P .
- ❖ Room temperature polarization with energy difference between polarized states increasing with electric field.



Ferroelectric 2H- α -In₂Se₃: Band Structure



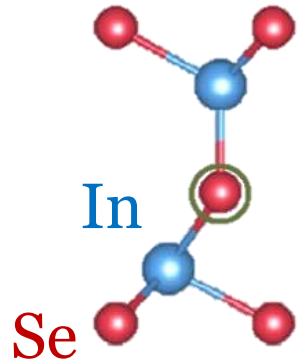
Inverted Mexican-Hat Valence Band, VB



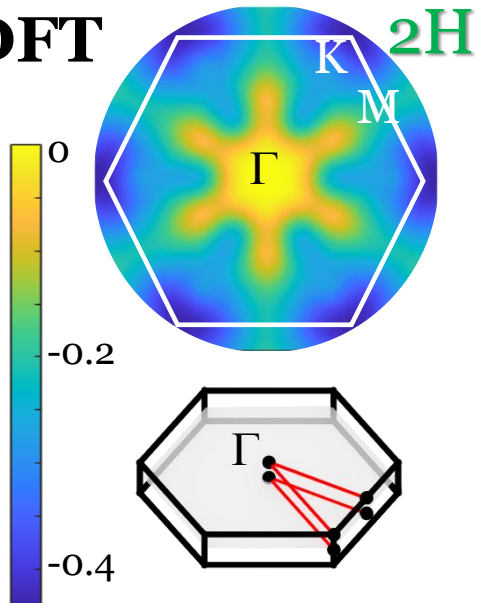
Felton et al.
Nature Com. 2025

Ferroelectric In_2Se_3 : Band structure

$\alpha\text{-In}_2\text{Se}_3$

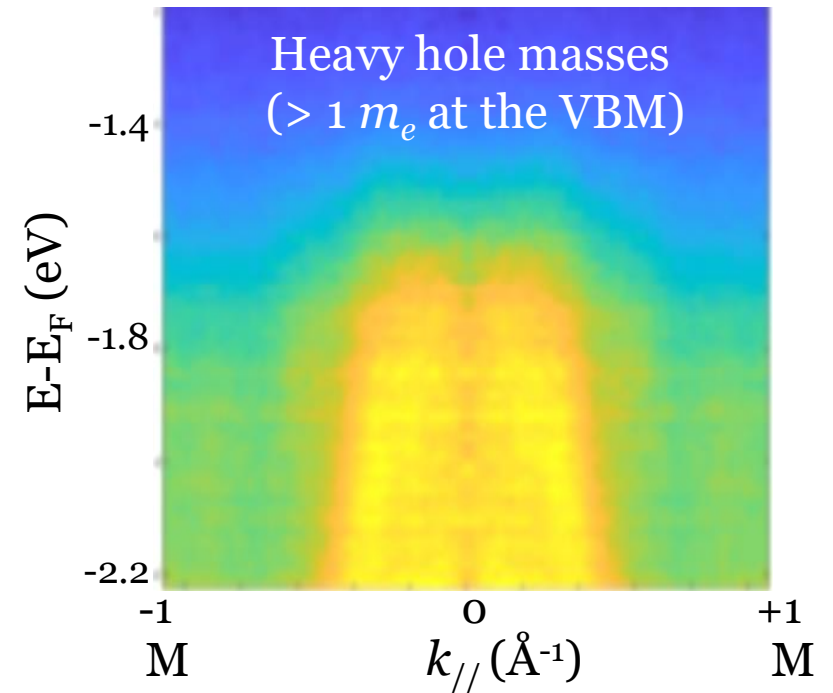
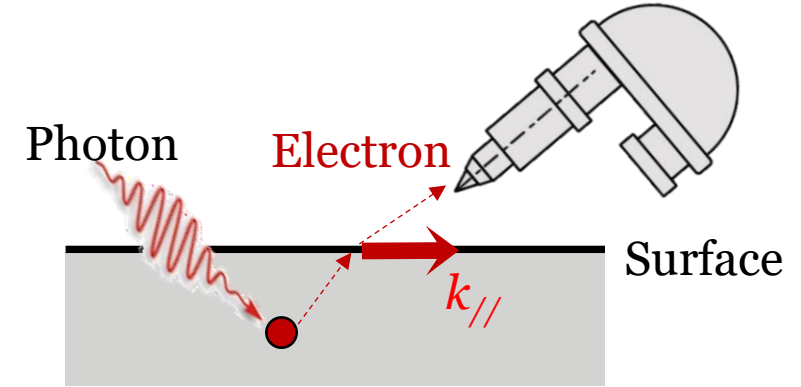
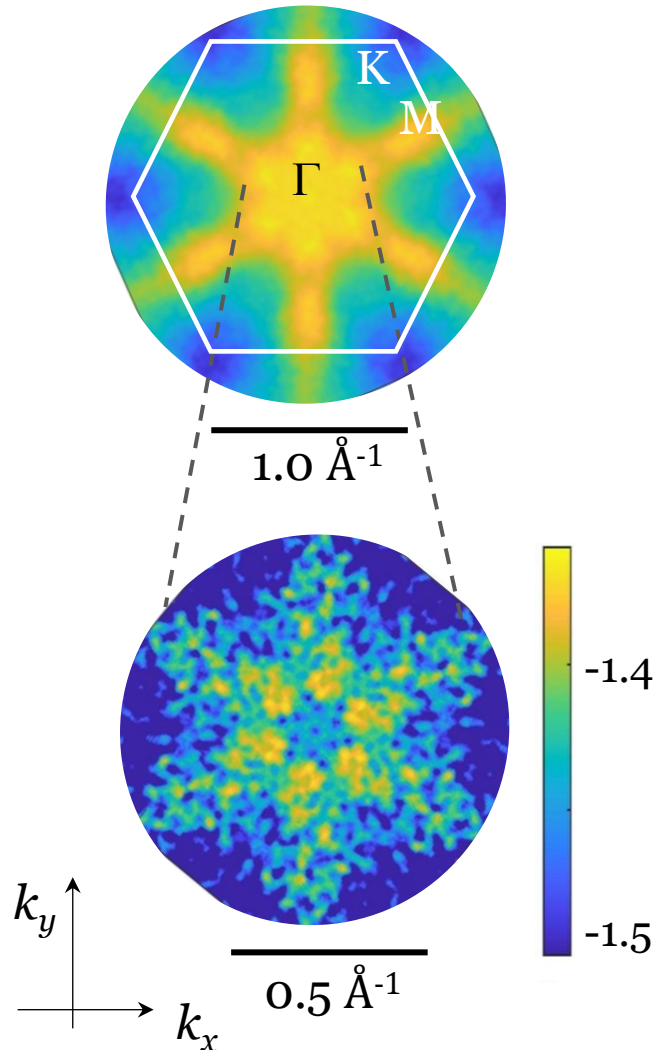


DFT



NanoARPES

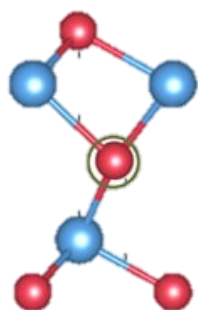
6 VB maxima along ΓM
6 saddle points along ΓK



Felton et al. *Nature Com.* 2025

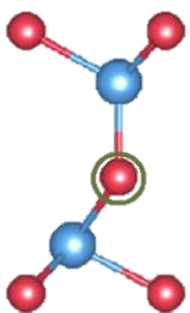
α -to- β Phase Transition

β - In_2Se_3

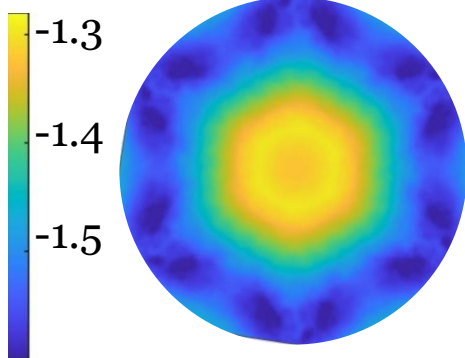


$T_a > 200\text{ }^\circ\text{C}$

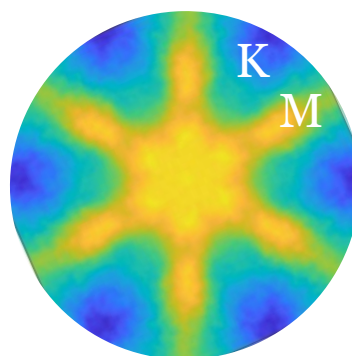
α - In_2Se_3



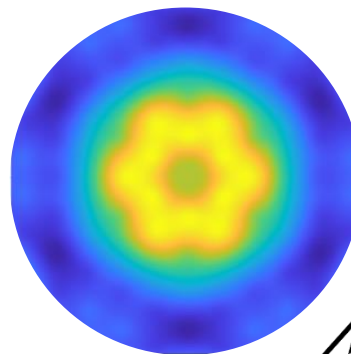
ARPES



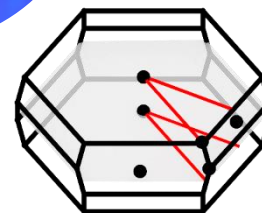
$T_a > 200\text{ }^\circ\text{C}$



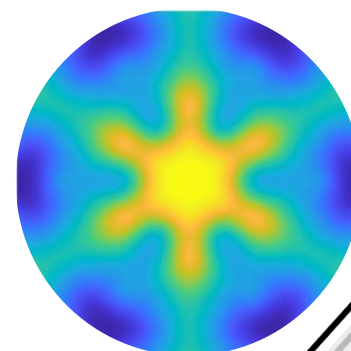
DFT



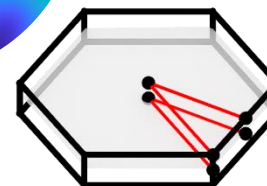
$3R$ - β



$1.0\text{ }\text{\AA}^{-1}$

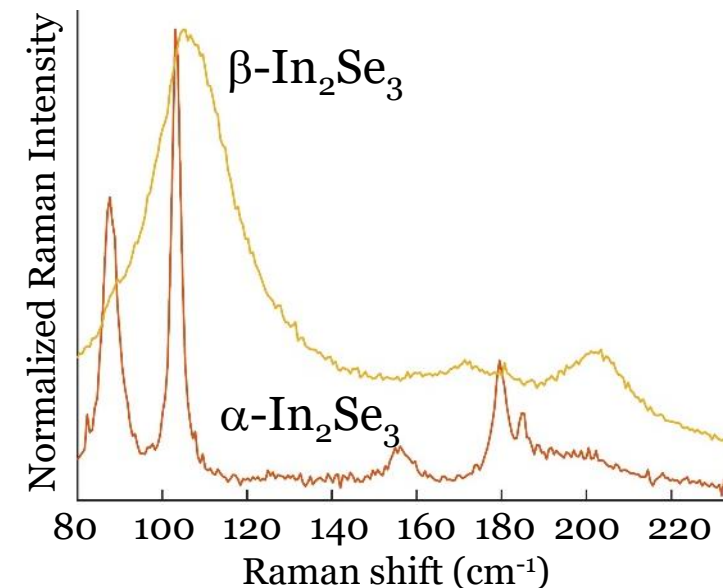


$2H$ - α

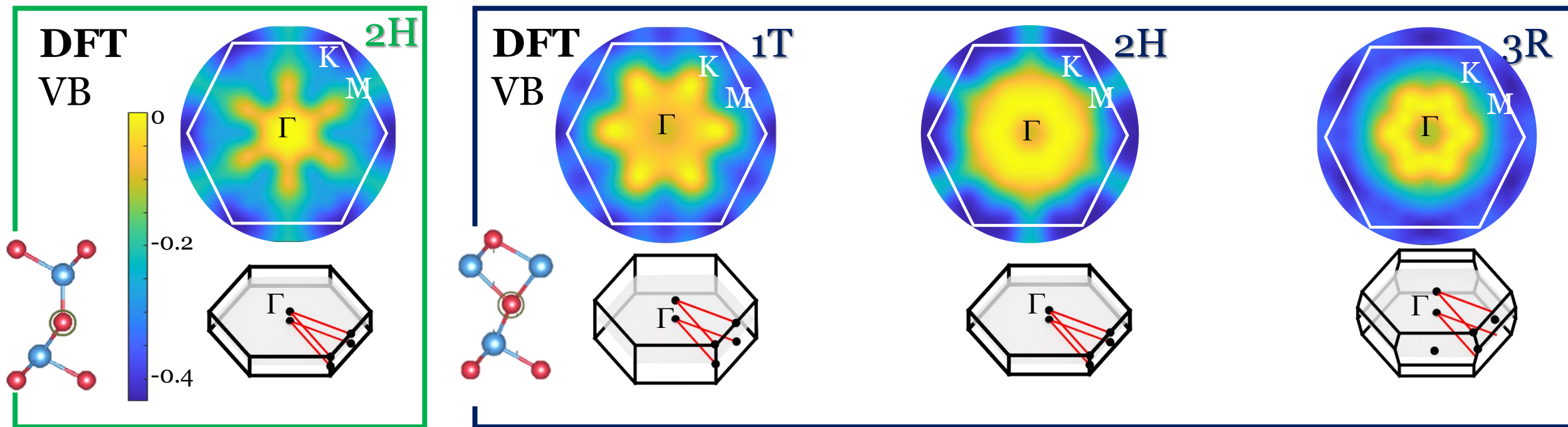


$1.0\text{ }\text{\AA}^{-1}$

- ❖ The β -phase is realized via a structural phase transition at $T_a > 200\text{ }^\circ\text{C}$ in UHV
- ❖ Raman spectroscopy to probe transition from β -phase to α -phase



Zoo of “Mexican Hat” VB



Felton et al. *Nature Com.* 2025

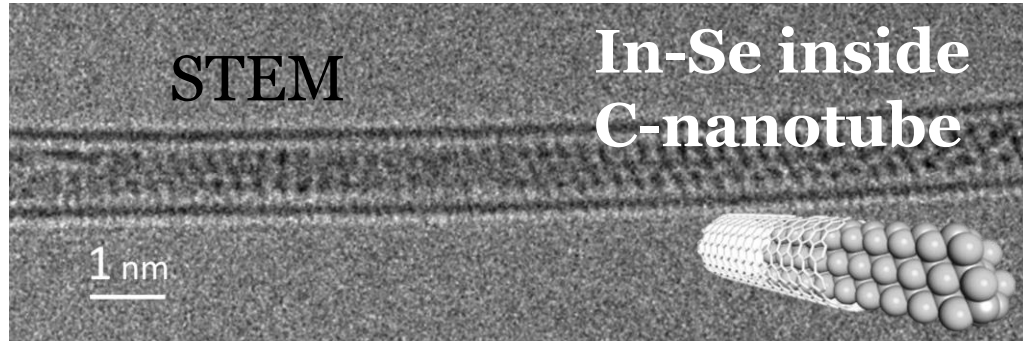
Opportunities: Muliferroic 2SEM

Hole doping can induce robust ferromagnetism in α - In_2Se_3 due to its flat Mexican-hat-shape VB with van Hove singularities. Hole doping can lead to time-reversal symmetry breaking with ferromagnetism and ferroelectricity within a wide range of doping concentrations.

Wang et al. *Adv Elec. Mat.* 2024

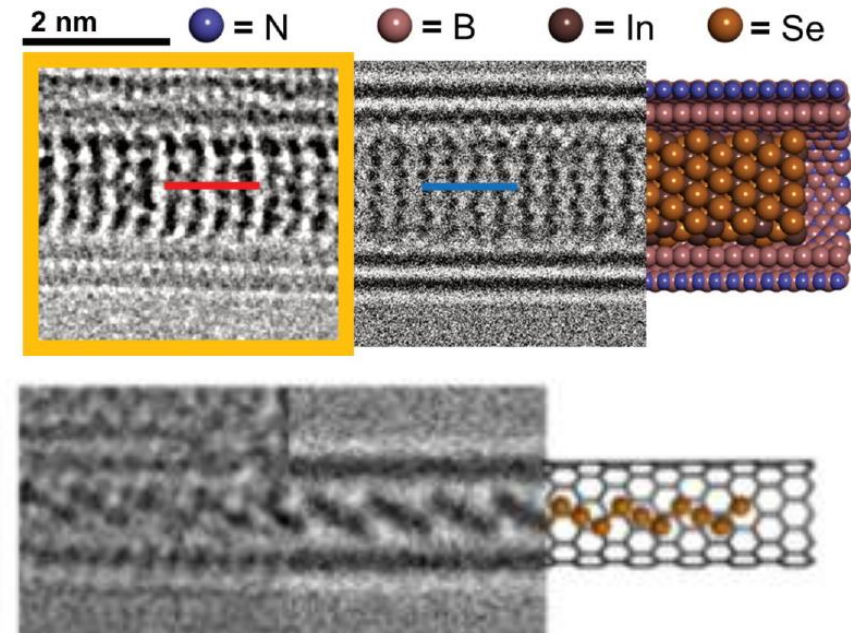
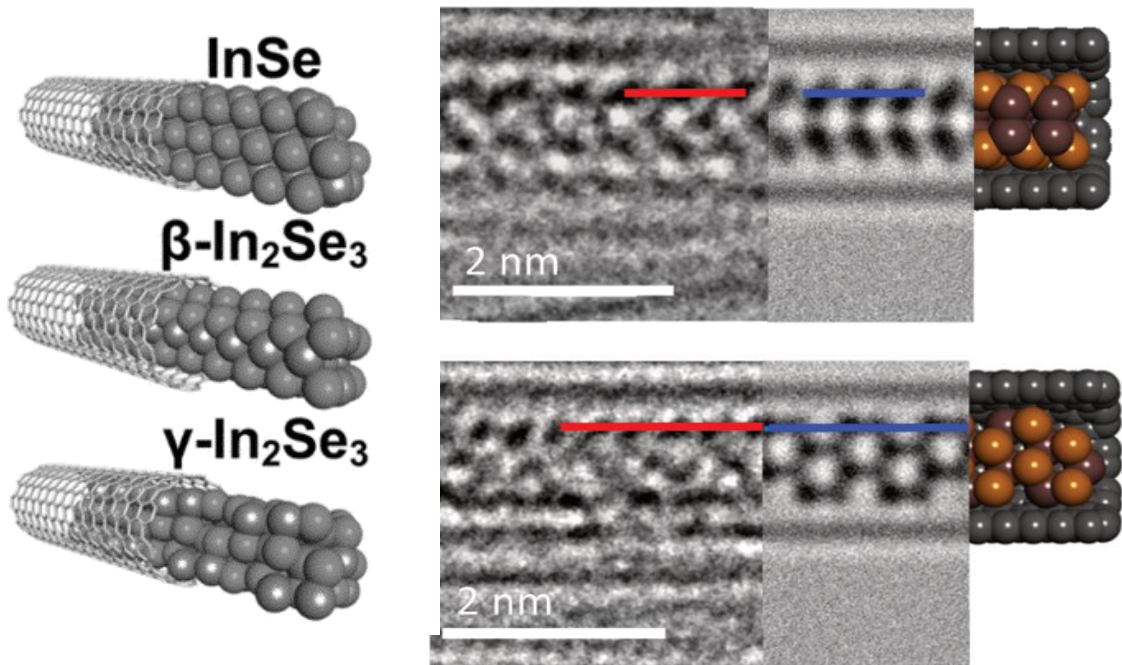
From 2D to 1D systems

Encapsulation of 2SEM within C and BN-nanotubes



A wide range of polymorphs and nanostructures

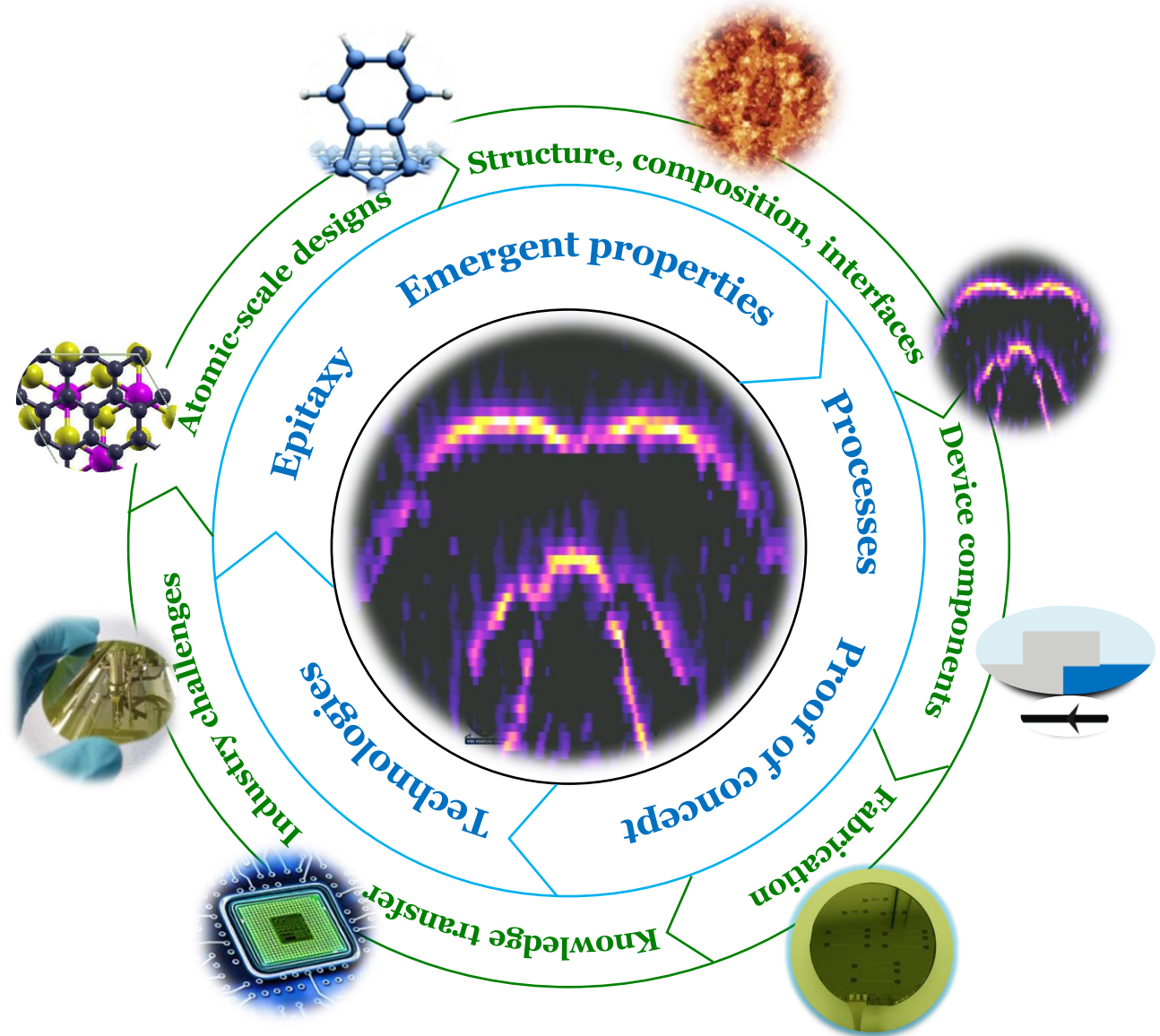
In-Se/Se inside a BN-nanotube



UK Research Programme: NEED2D

**EPSRC Programme Grant
2025-30, £6.3M**

- ❖ Queen Mary University of London, University of Glasgow and University of Nottingham will develop 2SEM for prototype low-energy consumption electronic devices that will reduce electricity demand from data centres/high-performance computing
- ❖ 2SEM produced at wafer-scale
- ❖ > 20 partners in academia/industry (Paragraf)





University of
Nottingham

UK China Malaysia



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N Cottam, B Dewes, K Rahman...*

Staff

*S Novikov, T Cheng,
PH Beton, CJ Mellor, J O'Shea,
L Eaves, O Makarovsky...*

...



Partners

